

**CERTIFICATION AND REQUEST FOR PRIORITIZED EXAMINATION
UNDER 37 CFR 1.102(e) (Page 1 of 1)**

First Named Inventor:	G.R. MOHAN Rao	Nonprovisional Application Number (if known):	
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS		

APPLICANT HEREBY CERTIFIES THE FOLLOWING AND REQUESTS PRIORITIZED EXAMINATION FOR THE ABOVE-IDENTIFIED APPLICATION.

1. The processing fee set forth in 37 CFR 1.17(i), the prioritized examination fee set forth in 37 CFR 1.17(c), and if not already paid, the publication fee set forth in 37 CFR 1.18(d) have been filed with the request. The basic filing fee, search fee, examination fee, and any required excess claims and application size fees are filed with the request or have been already been paid.
2. The application contains or is amended to contain no more than four independent claims and no more than thirty total claims, and no multiple dependent claims.
3. The applicable box is checked below:

I. ☒ Original Application (Track One) - Prioritized Examination under § 1.102(e)(1)

- i. (a) The application is an original nonprovisional utility application filed under 35 U.S.C. 111(a). This certification and request is being filed with the utility application via EFS-Web.
---OR---
(b) The application is an original nonprovisional plant application filed under 35 U.S.C. 111(a). This certification and request is being filed with the plant application in paper.
- ii. An executed oath or declaration under 37 CFR 1.63 is filed with the application.

II. ☐ Request for Continued Examination - Prioritized Examination under § 1.102(e)(2)

- i. A request for continued examination has been filed with, or prior to, this form.
- ii. If the application is a utility application, this certification and request is being filed via EFS-Web.
- iii. The application is an original nonprovisional utility application filed under 35 U.S.C. 111(a), or is a national stage entry under 35 U.S.C. 371.
- iv. This certification and request is being filed prior to the mailing of a first Office action responsive to the request for continued examination.
- v. No prior request for continued examination has been granted prioritized examination status under 37 CFR 1.102(e)(2).

Signature	/Gregory M. Howison, Reg. #30646/	Date	July 9, 2021
Name (Print/Typed)	Gregory M. Howison	Practitioner Registration Number	30,646
Note: Signatures of all the inventors or assignees of record of the entire interest or their representative(s) are required in accordance with 37 CFR 1.33 and 11.18. Please see 37 CFR 1.4(d) for the form of the signature. If necessary, submit multiple forms for more than one signature, see below*.			
☒ *Total of <u>ONE</u> forms are submitted.			

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The **Privacy Act of 1974 (P.L. 93-579)** requires that you be given certain information in connection with your submission of the attached form related to a patent application or patent. Accordingly, pursuant to the requirements of the Act, please be advised that: (1) the general authority for the collection of this information is 35 U.S.C. 2(b)(2); (2) furnishing of the information solicited is voluntary; and (3) the principal purpose for which the information is used by the U.S. Patent and Trademark Office is to process and/or examine your submission related to a patent application or patent. If you do not furnish the requested information, the U.S. Patent and Trademark Office may not be able to process and/or examine your submission, which may result in termination of proceedings or abandonment of the application or expiration of the patent.

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3. A record in this system of records may be disclosed, as a routine use, to a Member of Congress submitting a request involving an individual, to whom the record pertains, when the individual has requested assistance from the Member with respect to the subject matter of the record.
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6. A record in this system of records may be disclosed, as a routine use, to another federal agency for purposes of National Security review (35 U.S.C. 181) and for review pursuant to the Atomic Energy Act (42 U.S.C. 218(c)).
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9. A record from this system of records may be disclosed, as a routine use, to a Federal, State, or local law enforcement agency, if the USPTO becomes aware of a violation or potential violation of law or regulation.

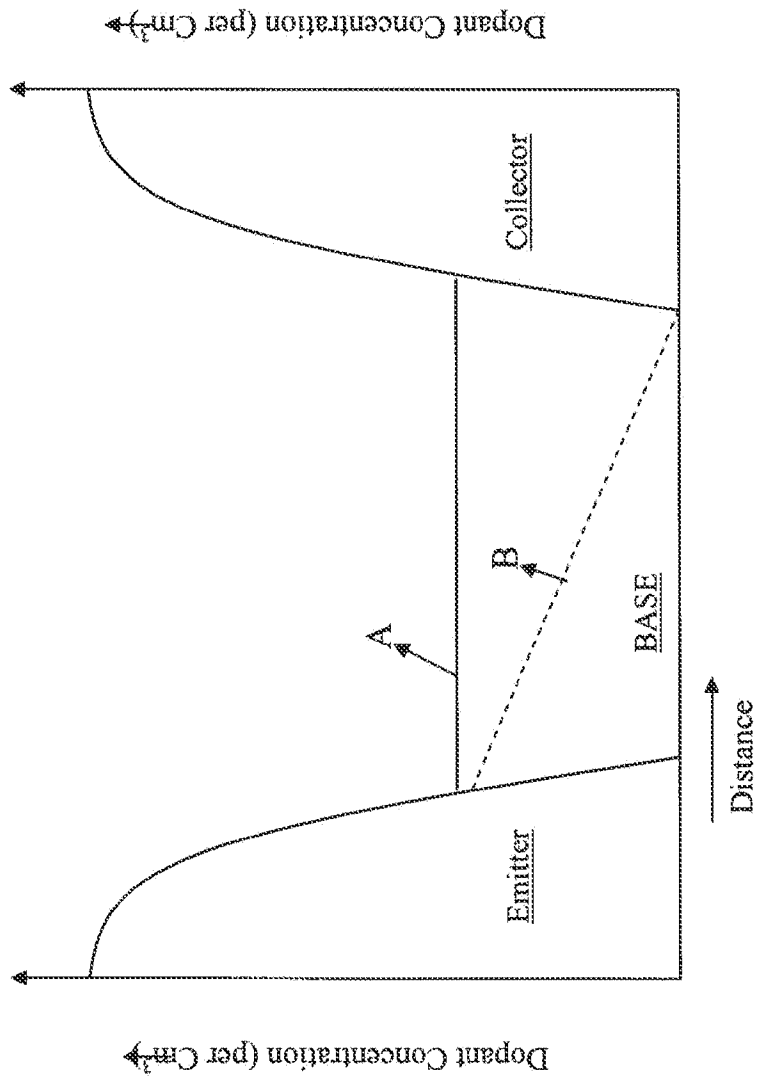


Figure 1 Prior Art

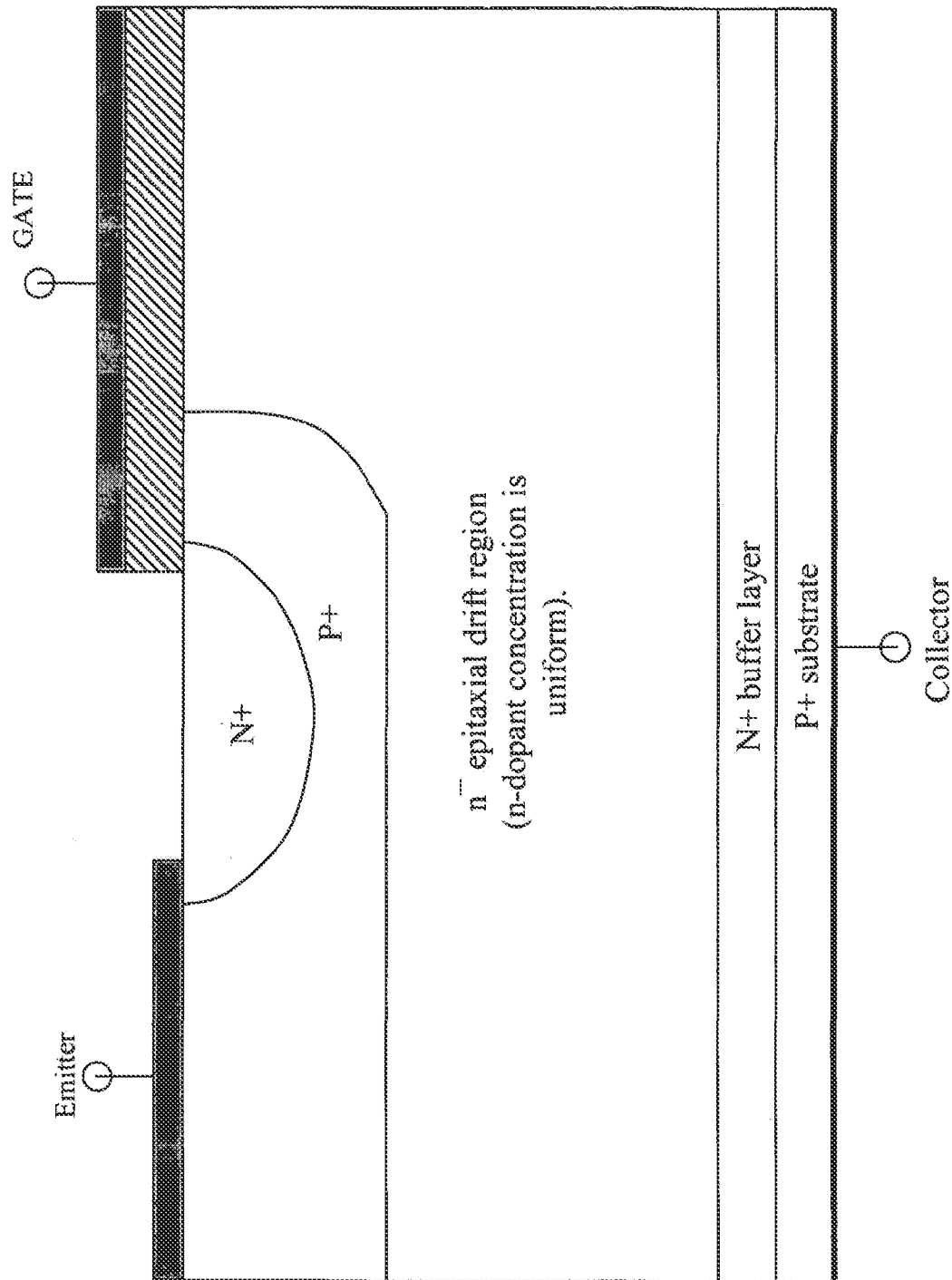


FIGURE 2 Prior art

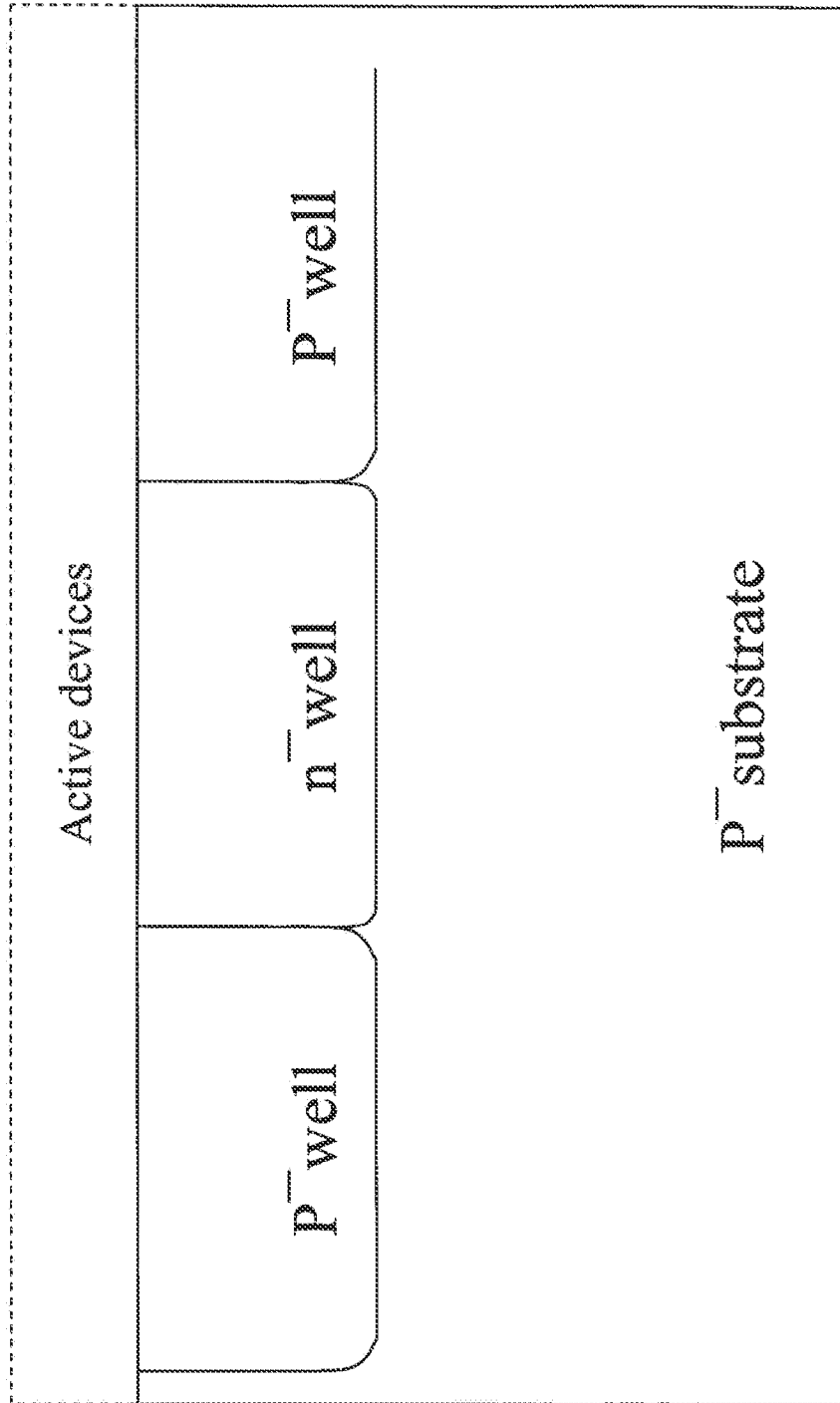


FIGURE 3A Prior art (Twin well CMOS) for a CMOS integrated circuit

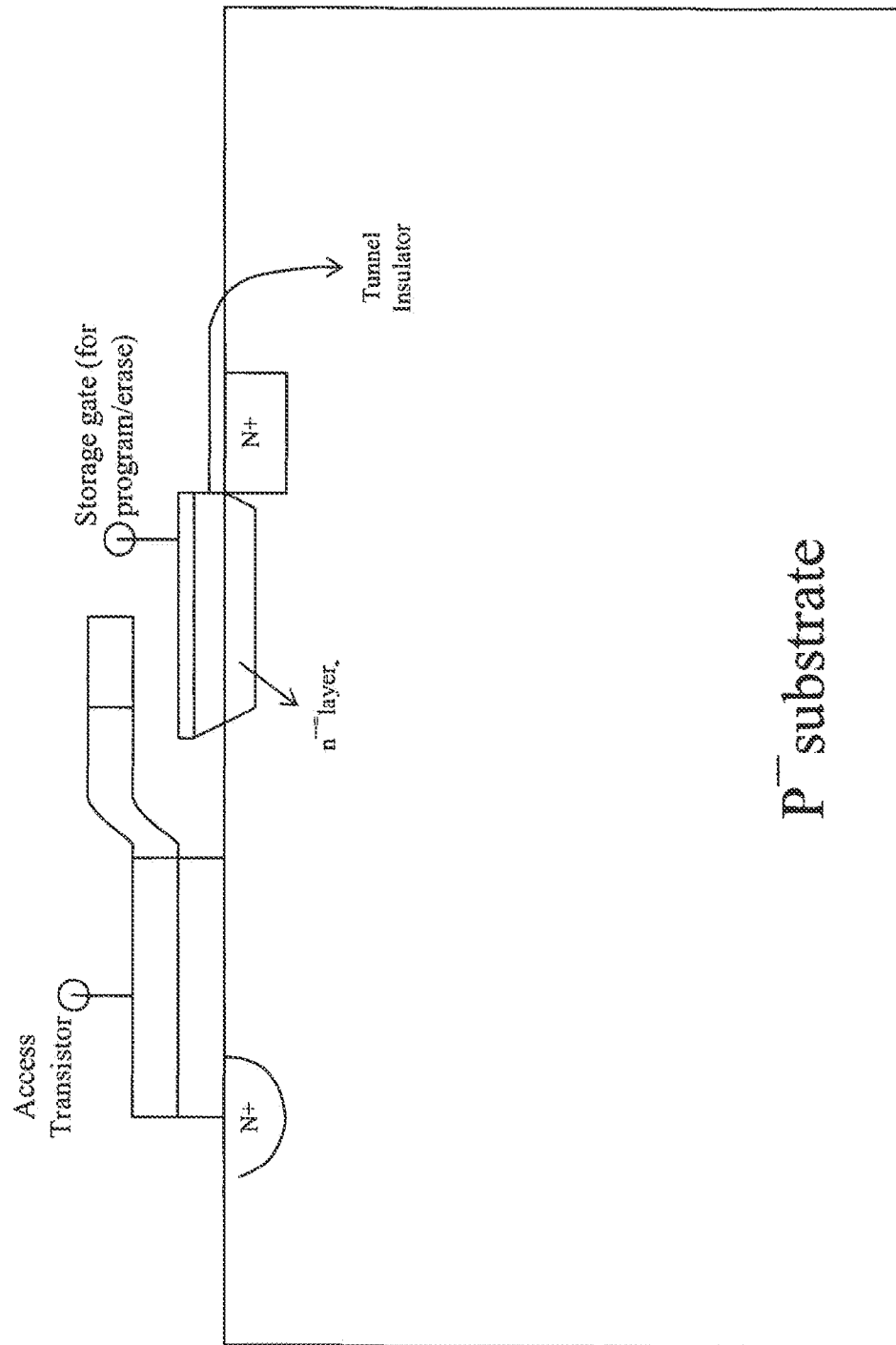


FIGURE 3B Prior art for a two-device EEPROM memory cell

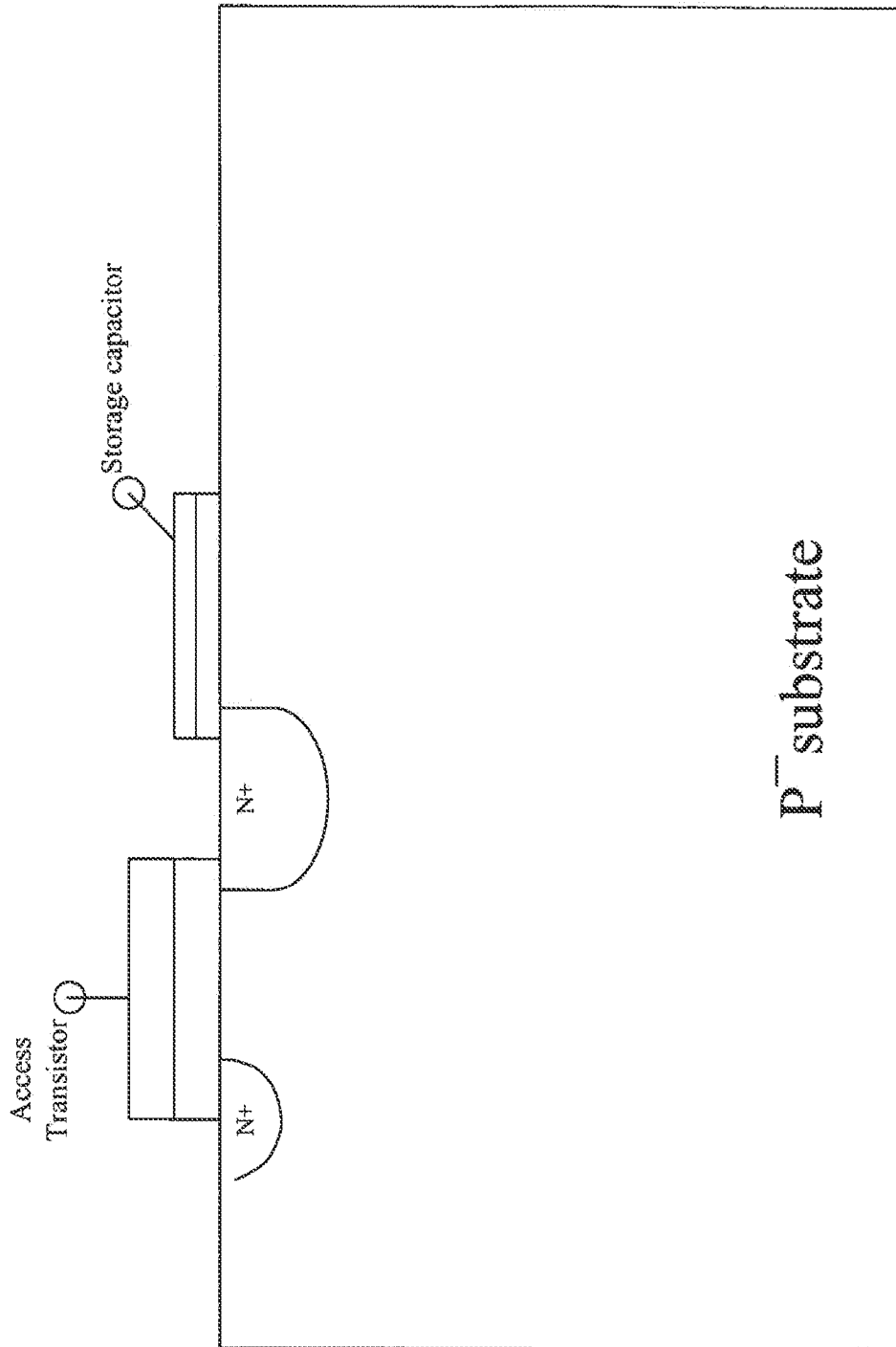


FIGURE 3C Prior art for a 1T-1C DRAM memory cell

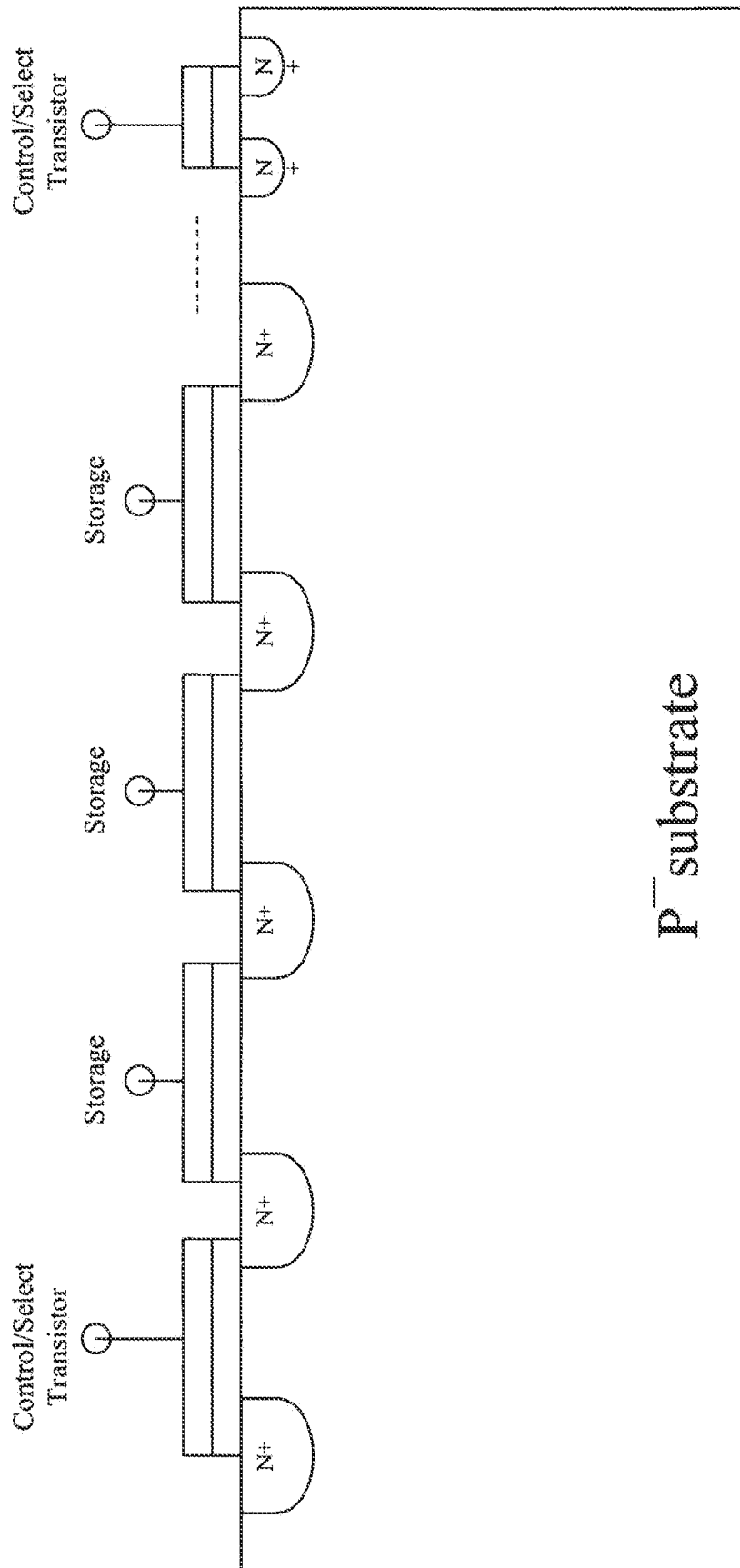


FIGURE 3D Prior art for a NAND flash memory cell

Note: Control/ Sect transistors have a single insulator - traditional MOS transistor.

Storage nodes have a stacked gate structure, typically with a floating gate and control gate comprising the stack.

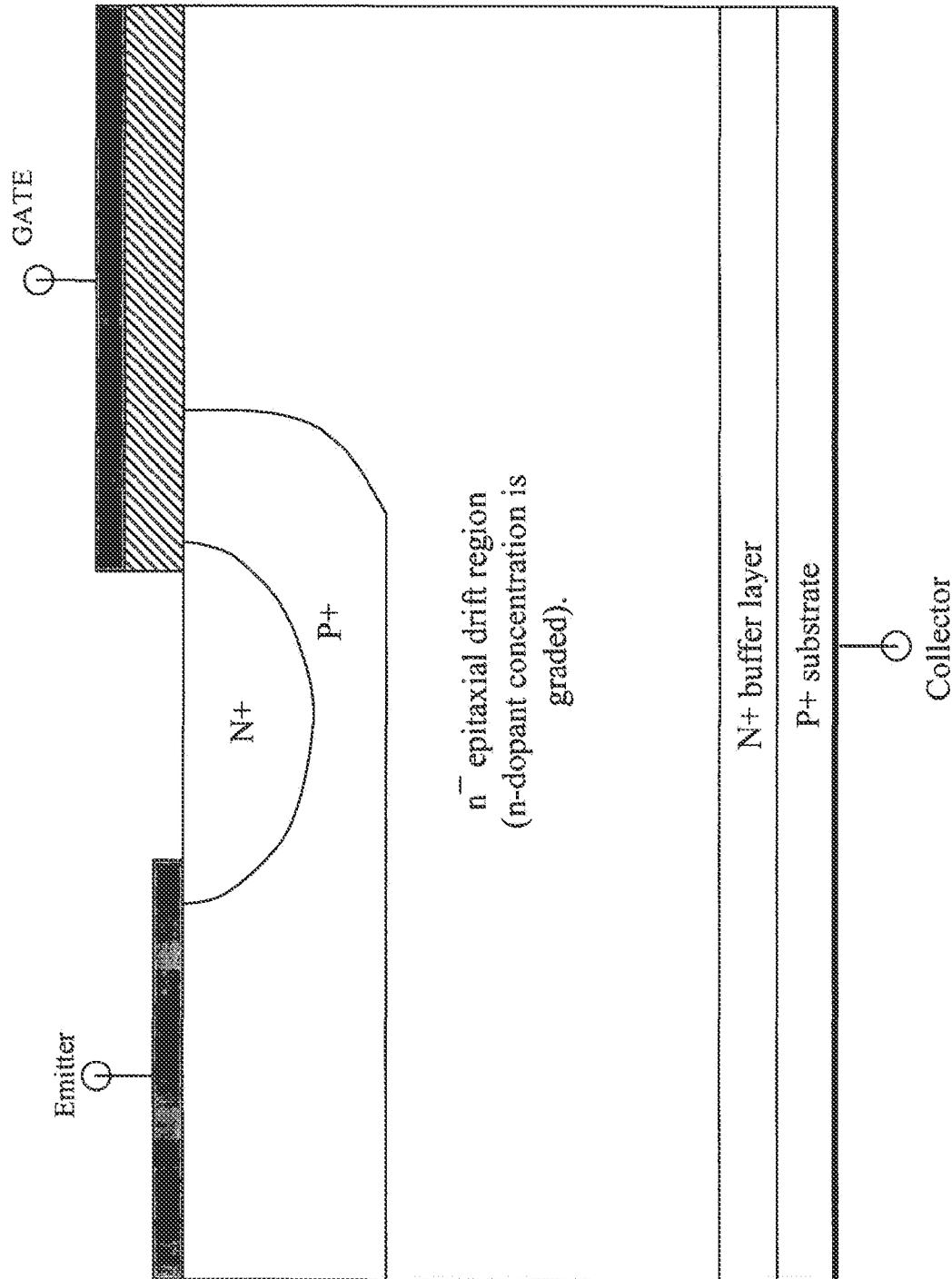


FIGURE 4 A dopant - concentration graded drift region in a IGBT

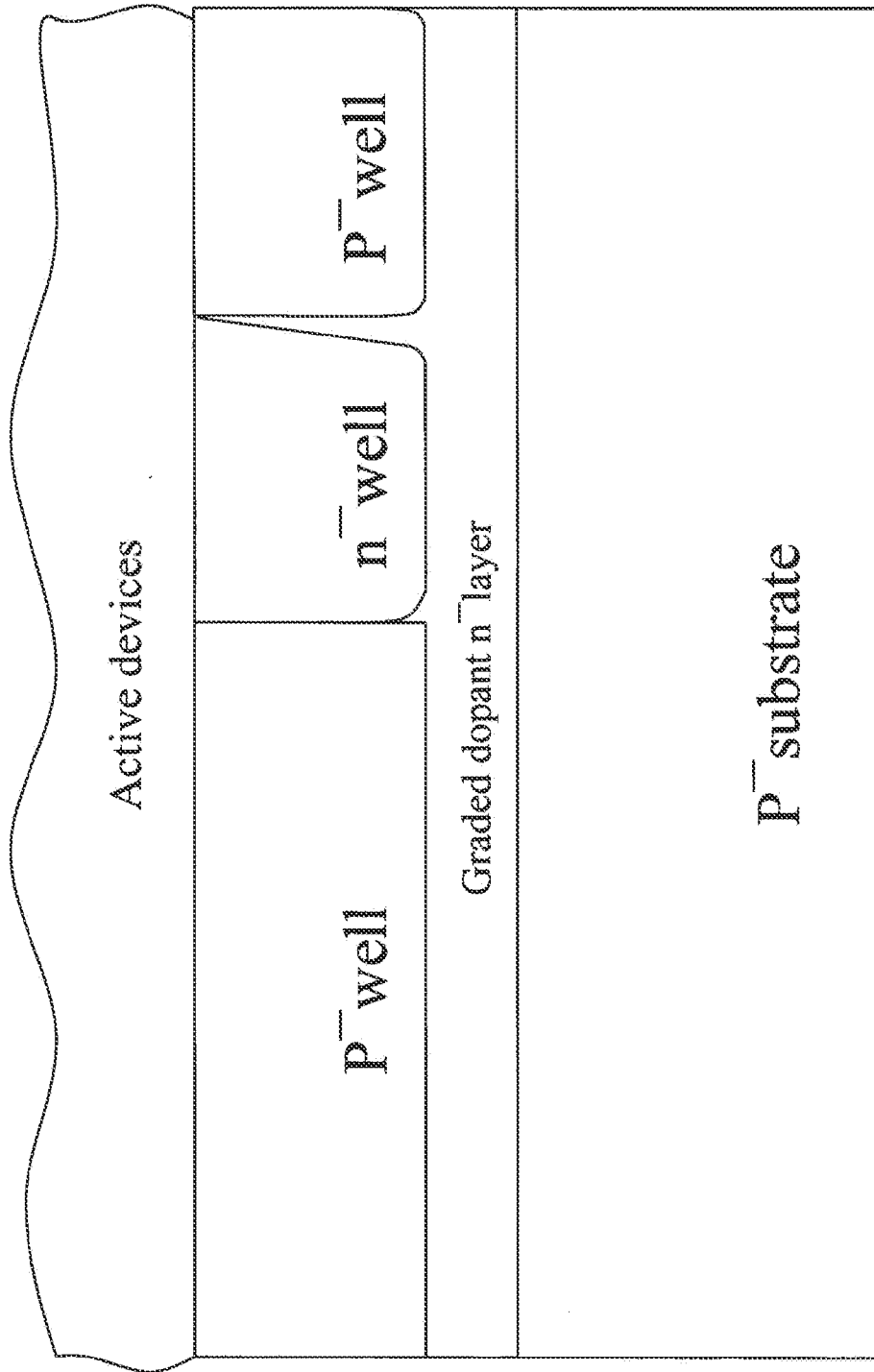


FIGURE 5A A CMOS Substrate for digital, mixed, signal, and sensors IC's

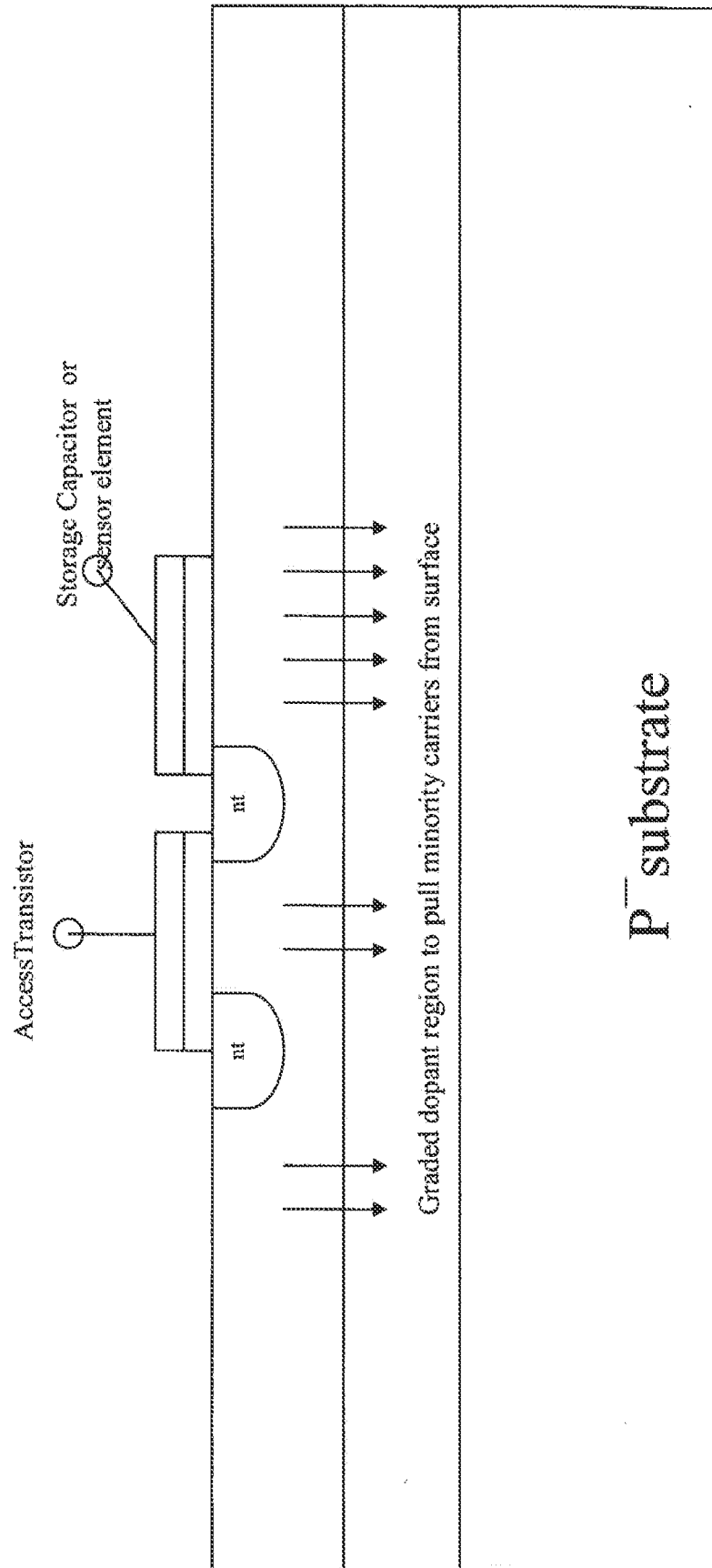


FIGURE 5B CMOS Substrate for a DRAM or image sensor, with one embodiment of the invention

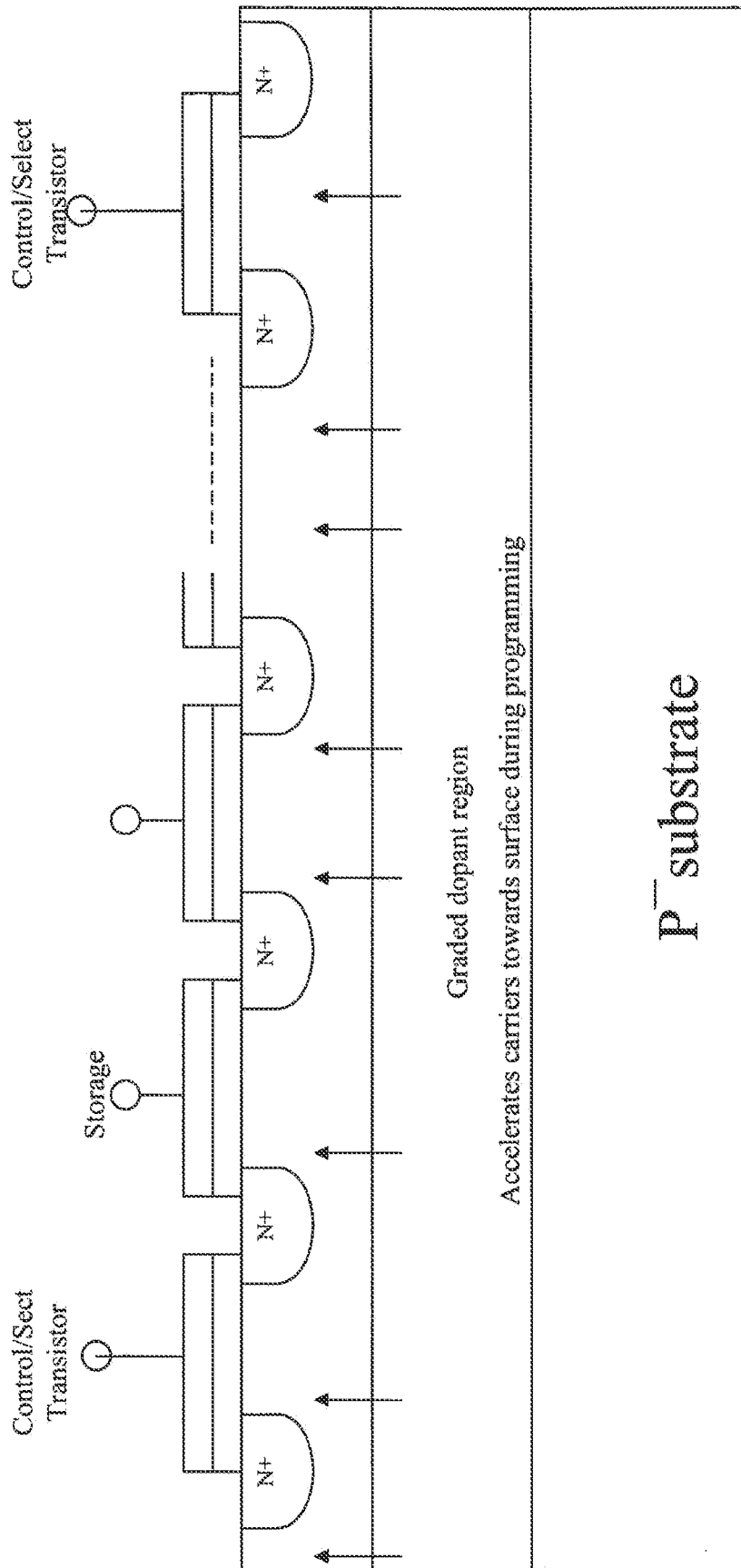


FIGURE 5C CMOS Substrate for a NAND flash device to improve programming times

TRANSMITTAL FOR POWER OF ATTORNEY TO ONE OR MORE REGISTERED PRACTITIONERS

NOTE: This form is to be submitted with the Power of Attorney by Applicant form (PTO/AIA/82B) to identify the application to which the Power of Attorney is directed, in accordance with 37 CFR 1.5, unless the application number and filing date are identified in the Power of Attorney by Applicant form. If neither form PTO/AIA/82A nor form PTO/AIA82B identifies the application to which the Power of Attorney is directed, the Power of Attorney will not be recognized in the application.

Application Number	
Filing Date	
First Named Inventor	G.R. MOHAN RAO
Title	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS
Art Unit	
Examiner Name	
Attorney Docket Number	GRTD60-35314

SIGNATURE of Applicant or Patent Practitioner

Signature	/Gregory M. Howison, Reg. #30646/	Date (Optional)	
Name	GREGORY M. HOWISON	Registration Number	30,646
Title (if Applicant is a juristic entity)			
Applicant Name (if Applicant is a juristic entity)			

NOTE: This form must be signed in accordance with 37 CFR 1.33. See 37 CFR 1.4(d) for signature requirements and certifications. If more than one applicant, use multiple forms.



*Total of ONE forms are submitted.

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I hereby revoke all previous powers of attorney given in the application identified in either the attached transmittal letter or the boxes below.

Application Number	Filing Date

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☒ I hereby appoint the Patent Practitioner(s) associated with the following Customer Number as my/our attorney(s) or agent(s), and to transact all business in the United States Patent and Trademark Office connected therewith for the application referenced in the attached transmittal letter (form PTO/AIA/82A) or identified above:

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I am the Applicant (if the Applicant is a juristic entity, list the Applicant name in the box):

GREENTHREAD, LLC

- ☐ Inventor or Joint Inventor (title not required below)
- ☐ Legal Representative of a Deceased or Legally Incapacitated Inventor (title not required below)
- ☒ Assignee or Person to Whom the Inventor is Under an Obligation to Assign (provide signer's title if applicant is a juristic entity)
- ☐ Person Who Otherwise Shows Sufficient Proprietary Interest (e.g., a petition under 37 CFR 1.46(b)(2) was granted in the application or is concurrently being filed with this document) (provide signer's title if applicant is a juristic entity)

SIGNATURE of Applicant for Patent

The undersigned (whose title is supplied below) is authorized to act on behalf of the applicant (e.g., where the applicant is a juristic entity).

Signature

Date (Optional)

Name

Title

GREENTHREAD, LLC

NOTE: Signature - This form must be signed by the applicant in accordance with 37 CFR 1.33. See 37 CFR 1.4 for signature requirements and certifications. If more than one applicant, use multiple forms.

☒ Total of ONE forms are submitted.

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**DECLARATION (37 CFR 1.63) FOR UTILITY OR DESIGN APPLICATION USING AN
APPLICATION DATA SHEET (37 CFR 1.76)****Title of
Invention****SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS**

As the below named inventor, I hereby declare that:

This declaration
is directed to:

The attached application, or



United States application or PCT International application number _____

filed on _____

The above-identified application was made or authorized to be made by me.

I believe that I am the original inventor or an original joint inventor of a claimed invention in the application.

I hereby acknowledge that any willful false statement made in this declaration is punishable under 18 U.S.C. 1001
by fine or imprisonment of not more than five (5) years, or both.**WARNING:**

Petitioner/applicant is cautioned to avoid submitting personal information in documents filed in a patent application that may contribute to identity theft. Personal information such as social security numbers, bank account numbers, or credit card numbers (other than a check or credit card authorization form PTO-2036 submitted for payment purposes) is never required by the USPTO to support a petition or an application. If this type of personal information is included in documents submitted to the USPTO, petitioners/applicants should consider redacting such personal information from the documents before submitting them to the USPTO. Petitioner/applicant is advised that the record of a patent application is available to the public after publication of the application (unless a non-publication request in compliance with 37 CFR 1.213(a) is made in the application) or issuance of a patent. Furthermore, the record from an abandoned application may also be available to the public if the application is referenced in a published application or an issued patent (see 37 CFR 1.14). Checks and credit card authorization forms PTO-2036 submitted for payment purposes are not retained in the application file and therefore are not publicly available.

LEGAL NAME OF INVENTORInventor: G.R. Mohan RaoDate (Optional): Sept 30, 2015Signature: G.R. Mohan Rao

Note: An application data sheet (PTO/AIA/14 or equivalent), including naming the entire inventive entity, must accompany this form.
Use an additional PTO/SB/AIA01 form for each additional inventor.

This collection of information is required by 35 U.S.C. 115 and 37 CFR 1.63. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.11 and 1.14. This collection is estimated to take 1 minute to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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ABSTRACT

Most semiconductor devices manufactured today, have uniform dopant concentration, either in the lateral or vertical device active (and isolation) regions. By grading the dopant concentration, the performance in various semiconductor devices can be significantly improved. Performance improvements can be obtained in application specific areas like increase in frequency of operation for digital logic, various power MOSFET and IGBT ICs, improvement in refresh time for DRAMs, decrease in programming time for nonvolatile memory, better visual quality including pixel resolution and color sensitivity for imaging ICs, better sensitivity for varactors in tunable filters, higher drive capabilities for JFETs, and a host of other applications.

WHAT IS CLAIMED IS:

1. A VLSI semiconductor device, comprising:
 - a substrate of a first doping type at a first doping level having a surface;
 - a first active region disposed adjacent the surface with a second doping type opposite in conductivity to the first doping type and within which transistors can be formed;
 - 5 a second active region separate from the first active region disposed adjacent to the first active region and within which transistors can be formed;
 - transistors formed in at least one of the first active region or second active region;
 - at least a portion of at least one of the first and second active regions having at least one graded dopant concentration to aid carrier movement from the first and second active
 - 10 regions towards an area of the substrate where there are no active regions; and
 - at least one well region adjacent to the first or second active region containing at least one graded dopant region, the graded dopant region to aid carrier movement from the surface towards the area of the substrate where there are no active regions, wherein at least some of the transistors form digital logic of the VLSI semiconductor device.
2. The VLSI semiconductor device of Claim 1, wherein the substrate is a p-type substrate.
3. The VLSI semiconductor device of Claim 1, wherein the substrate has epitaxial silicon on top of a non-epitaxial substrate.
4. The VLSI semiconductor device of Claim 1, wherein the first active region and second active region contain digital logic formed by one of either p-channel and n-channel devices.
5. The VLSI semiconductor device of Claim 1, wherein the first active region and second active region contain either p-channel or n-channel devices in n-wells or p-wells, respectively, and each well has at least one graded dopant.
6. The VLSI semiconductor device of Claim 1, wherein the first active region and second active region are each separated by at least one isolation region.

7. The VLSI semiconductor device of Claim 1, wherein the graded dopant is fabricated with an ion implantation process.
8. The VLSI semiconductor device of Claim 1, wherein the first and second active regions are formed adjacent the first surface of the substrate.
9. The VLSI semiconductor device of Claim 1, wherein dopants of the graded dopant concentration in the first active region or the second active region are either p-type or n-type.
10. The VLSI semiconductor device of Claim 1, wherein dopants of the graded dopant concentration in the first active region are both p-type and n-type.
11. The VLSI semiconductor device of Claim 1, wherein dopants of the graded dopant concentration in the second active region are both p-type and n-type.
12. The VLSI semiconductor device of Claim 1, wherein dopants of the graded dopant region in the well region are both p-type and n-type.
13. The VLSI semiconductor device of claim 1, wherein the transistors which can be formed in the first and second active regions are CMOS digital logic transistors requiring at least a source, a drain, a gate and a channel.
14. The VLSI semiconductor device of Claim 1, wherein the device is a dynamic random access memory (DRAM).
15. The VLSI semiconductor device of Claim 1, wherein the device is a complementary metal oxide semiconductor (CMOS) with a nonepitaxial substrate.
16. The VLSI semiconductor device of Claim 1, wherein the device is a flash memory.
17. The VLSI semiconductor device of Claim 1, wherein the device comprises digital logic and capacitors.
18. The VLSI semiconductor device of Claim 1, wherein the device is central processing unit.

19. The VLSI semiconductor device of Claim 1, wherein the device is an image sensor.

20. The VLSI semiconductor device of Claim 1, wherein each of the first and second active regions are in the lateral or vertical direction.

21. A VLSI semiconductor device, comprising:

a substrate of a first doping type at a first doping level having a surface;

a first active region disposed adjacent the surface of the substrate with a second doping type opposite in conductivity to the first doping type and within which transistors can be formed in the surface thereof;

a second active region separate from the first active region disposed adjacent to the first active region and within which transistors can be formed in the surface thereof;

transistors formed in at least one of the first active region or second active region;

at least a portion of at least one of the first and second active regions having at least one graded dopant concentration to aid carrier movement from the surface to an area of the substrate where there are no active regions; and

at least one well region adjacent to the first or second active region containing at least one graded dopant region, the graded dopant region to aid carrier movement from the surface to the area of the substrate where there are no active regions, and wherein the graded dopant concentration is linear, quasilinear, error function, complementary error function, or any combination thereof.

22. The VLSI semiconductor device of Claim 21, wherein the substrate is an n-type substrate.

23. The VLSI semiconductor device of Claim 21, wherein the substrate is a p-type substrate.

24. The VLSI semiconductor device of Claim 21, wherein the substrate has epitaxial silicon on top of a nonepitaxial substrate.

25. The VLSI semiconductor device of Claim 21, wherein the first active region and second active region contain at least one of either p-channel and n-channel devices.

26. The VLSI semiconductor device of Claim 21, wherein the first active region and second active region contain either p-channel or n-channel devices in n-wells or p-wells, respectively, and each well has at least one graded dopant.
27. The VLSI semiconductor device of Claim 21, wherein the first active region and second active region are each separated by at least one isolation region.
28. The VLSI semiconductor device of Claim 21, wherein dopants of the graded dopant concentration in the first active region or the second active region are either p-type or n-type.
29. The VLSI semiconductor device of Claim 21, wherein dopants of the graded dopant concentration in the first active region are both p-type and n-type.
30. The VLSI semiconductor device of Claim 21, wherein dopants of the graded dopant concentration in the second active region are both p-type and n-type.

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE
APPLICATION FOR UNITED STATES PATENT**

SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS

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Attorneys:

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS****CROSS-REFERENCE TO RELATED APPLICATIONS**

[0001] This application is a Continuation of U.S. Patent Application No. 16/947,294, filed July 27, 2020, entitled SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS, which is a Continuation of U.S. Patent Application No. 16/717,950, filed December 17, 2019, entitled SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS, issued as U.S. Patent No. 10,734,481 on August 04, 2020. U.S. Patent Application No. 16/717,950 is a Continuation of U.S. Patent Application No. 15/590,282, filed May 9, 2017, entitled SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS, issued as U.S. Patent No. 10,510, 842 on December 17, 2019, which is a Continuation of U.S. Patent Application No. 14/931,636, filed November 3, 2015, entitled SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS, issued as U.S. Patent No. 9,647,070 on May 9, 2017, which is Continuation of U.S. Patent Application No. 14/515,584, filed October 16, 2014, entitled SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS, issued as U.S. Patent No. 9,190,502 on November 17, 2015, which is a Continuation of U.S. Patent Application No. 13/854,319 filed April 1, 2013, entitled SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS, which is a Continuation of 11/622,496, filed January 12, 2007, entitled SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS, issued as U.S. Patent No. 8,421,195 on April 16, 2013, which is a Divisional of U.S. Patent Application No. 10/934,915, filed September 3, 2004. The disclosures of which are incorporated herein by reference in their entirety.

TECHNICAL FIELD

[0002] This present invention relates to all semiconductor devices and systems. Particularly it applies to diffused diodes, avalanche diodes, Schottky devices, power MOS transistors, JFET's, RF bipolar transistors, IGBTs (Insulated Gate Bipolar Transistors), varactors, digital VLSI, mixed signal circuits and sensor devices including camera ICs employing CCD (Charge Coupled Device) as well as CMOS technologies.

BACKGROUND

[0003] Bipolar Junction Transistors (BJT) are classified as minority carrier devices because minority carriers are the principle device conduction mechanism. However, majority carriers also play a small but finite role in modulating the conductivity in BJTs. Consequently, both carriers (electrons and holes) play a role in the switching performance of BJTs. The maximum frequency of operation in BJTs is limited by the base transit time as well as the quick recombination of the majority carriers when the device is switched off (prior to beginning the next cycle). The dominant carrier mechanism in BJTs is carrier diffusion. The carrier drift current component is fairly small, especially in uniformly doped base BJTs. Efforts have been made in graded base transistors to create an aiding drift field to enhance the diffusing minority carrier's speed from emitter to collector. However, most semiconductor devices, including various power MOSFETs (traditional, DMOS, lateral, vertical and a host of other configurations), IGBT's (Insulated Gated Base Transistors), still use a uniformly doped 'drift epitaxial' region in the base. FIG. 1 shows the relative doping concentration versus distance in a BJT. FIG. 2 shows the uniformly doped epi region in an IGBT. In contrast to BJTs, MOS devices are majority carrier devices for conduction. The conduction is channel dominated. The channel can be a surface in one plane in planar devices. The surface can also be on the sidewalls in a vertical device. Other device architectures to combine planar and vertical conductions are also possible. The maximum frequency of operation is dictated primarily by source-drain separation distance. Most MOS devices use a uniformly doped substrate (or a well region). When a MOSFET is optimally integrated with a BJT in a monolithic fashion, an IGBT results. The IGBT inherits the advantages of both MOSFET and BJT. It also brings new challenges because the required characteristics (electron transit and hole recombination as fast as possible in n-channel IGBT) necessitate different dopant gradients either in the same layer at different positions, or at the interfaces of similar or dissimilar layers.

[0004] Retrograde wells have been attempted, with little success, to help improve soft error immunity in SRAMs and visual quality in imaging circuits. FIG. 3A shows a typical CMOS VLSI device employing a twin well substrate, on which active devices are subsequently fabricated. FIGS. 3B, 3C, and 3D illustrate device cross sections, as practiced today. Retrograde and halo wells have also been attempted to improve refresh time in DRAMs (dynamic random-access memories), as well as, reducing dark current (background noise) and enhance RGB (Red, Green,

Blue) color resolution in digital camera ICs. Most of these techniques either divert the minority carriers away from the active regions of critical charge storage nodes at the surface, or, increase minority carrier density locally as the particular application requires.

BRIEF DESCRIPTION OF THE DRAWINGS

[0005] For a more complete understanding of the present invention, and the advantages thereof, reference is now made to the following descriptions taken in conjunction with the accompanying drawings, in which:

[0006] FIG. 1 illustrates the relative doping profiles of emitter, base and collector for the two most popular bipolar junction transistors: namely, uniform base (“A”) and graded base (“B”);

[0007] FIG. 2 illustrates the cross section of a commercial IGBT with a uniform epitaxial drift region (base);

[0008] FIGS. 3A, 3B, 3C, and 3D illustrate cross sections of commonly used prior art CMOS silicon substrates; FIG. 3A showing a typical prior art IC with two wells (one n⁻well in which p-channel transistors are subsequently fabricated and one p⁻well in which n-channel transistors are subsequently fabricated); FIG. 3B showing a prior art EEPROM (Electrically Erasable Programmable Read-Only Memory) memory cell having a tunnel insulator; FIG. 3C showing a prior art DRAM memory cell; and FIG. 3D showing a prior art NAND flash memory cell;

[0009] FIG. 4 illustrates the cross section of an IGBT, using one embodiment of the invention described here, where the dopant is optimally graded in the epitaxial drift region; and

[0010] FIGS. 5A, 5B, and 5C illustrate the cross sections of a CMOS silicon substrate with two wells and an underlying layer using embodiments of the invention to improve performance in each application—VLSI logic, DRAM/image IC, nonvolatile memory IC.

DETAILED DESCRIPTION

[0011] The relative doping concentrations of emitter and collector regions varies from 10^{18} to $10^{20}/\text{cm}^3$, whereas the base region is 10^{14} to $10^{16}/\text{cm}^3$ depending on the desired characteristics of the BJT. In graded base p-n-p transistors, the donor dopant concentration may be 10 to $100\times$ at the emitter-base junction, relative to the base-collector junction ($1\times$). The gradient can be linear, quasi linear, exponential or complimentary error function. The relative slope of the donor concentration throughout the base creates a suitable aiding drift electric field, to help the holes (p-n-p transistor) transverse from emitter to collector. Since the aiding drift electric field helps hole conduction, the current gain at a given frequency is enhanced, relative to a uniformly-doped (base) BJT. The improvement in cut-off frequency (or, frequency at unity gain, f_T) can be as large as $2\times$ - $5\times$. Similar performance improvements are also applicable to n-p-n transistors.

[0012] As illustrated in FIG. 4, in one embodiment according to the invention, a donor gradient is established from the emitter-drift epitaxial base region junction of the punch-through IGBT, to the drift epitaxial base region— n^+ buffer layer boundary (electrons in this case are accelerated in their transit from emitter to collector). The “average” base resistance is optimized so that conductivity modulation and lifetime (for minority carriers) in the base region are not compromised. By sweeping the carriers towards the n^+ buffer region a number of advantages are obtained. First, the frequency of operation (combination of t_{on} and t_{off} as is known in the IGBT commercial nomenclature) can be enhanced. Second, and maybe more importantly, during t_{off} , holes can be recombined much quicker at the n^+ buffer layer, compared to the uniformly doped n^- epitaxial drift region by establishing a different dopant gradient near the n^+ buffer layer. It should be noted that the drift region can also be a non-epitaxial silicon substrate. Although epitaxy enhances lifetime, it is not mandatory. Different layers of dopant regions can be transferred through wafer to wafer bonding (or other similar transfer mechanisms) for eventual device fabrication. The “reverse recovery time” for an IGBT is significantly improved due to the optimized graded dopant in the so called “drift region” as well as at the interfaces of the drift region. Graded dopants can also be implemented in the n^+ buffer layer as well as other regions adjacent to the respective layers. Two important performance enhancements are the result of dopant gradients. For example, in an n-channel IGBT, electrons can be swept from source to drain rapidly, while at the same time holes can be recombined closer to the n^+ buffer layer. This can improve t_{on} and t_{off} in the same device.

[0013] As illustrated in FIGS. 5A, 5B, and 5C, donor gradient is also of benefit to very large scale integrated circuits (VLSI)—VLSI logic, DRAM, nonvolatile memory like NAND flash. Spurious minority carriers can be generated by clock switching in digital VLSI logic and memory ICs. These unwanted carriers can discharge dynamically-held “actively held high” nodes. In most cases, statically-held nodes (with V_{cc}) cannot be affected. Degradation of refresh time in DRAMs is one of the results, because the capacitor holds charge dynamically. Similarly, degradation of CMOS digital images in digital imaging ICs is another result of the havoc caused by minority carriers. Pixel and color resolution can be significantly enhanced in imaging ICs with the embodiments described herein. Creating “subterranean” recombination centers underneath the wells (gold doping, platinum doping) as is done in some high-voltage diodes is not practical for VLSI circuits. Hence, a novel technique is described herein which creates a drift field to sweep these unwanted minority carriers from the active circuitry at the surface into the substrate in a monolithic die as quickly as possible. In a preferred embodiment, the subterranean n^- layer has a graded donor concentration to sweep the minority carriers deep into the substrate. One or more of such layers can also be implemented through wafer to wafer bonding or similar “transfer” mechanisms. This n^- layer can be a deeply-implanted layer. It can also be an epitaxial layer. As desired, the n^- well and p^- wells can also be graded or retrograded in dopants to sweep those carriers away from the surface as well. The graded dopant can also be implemented in surface channel MOS devices to accelerate majority carriers towards the drain. To decrease programming time in nonvolatile memory devices, carriers should be accelerated towards the surface when programming of memory cells is executed. The graded dopant can also be used to fabricate superior Junction Field-Effect transistors where the “channel pinch-off” is controlled by a graded channel instead of a uniformly doped channel (as practiced in the prior art).

[0014] One of ordinary skill and familiarity in the art will recognize that the concepts taught herein can be customized and tailored to a particular application in many advantageous ways. For instance, minority carriers can be channeled to the surface to aid programming in nonvolatile memory devices (NOR, NAND, multivalued-cell). Moreover, single-well, and triple-well CMOS fabrication techniques can also be optimized to incorporate these embodiments individually and collectively. Any modifications of such embodiments (described here) fall within the spirit and scope of the invention. Hence, they fall within the scope of the claims described below.

[0015] Although the invention has been described with reference to specific embodiments, these descriptions are not meant to be construed in a limiting sense. Various modifications of the disclosed embodiments, as well as alternative embodiments of the invention will become apparent to persons skilled in the art upon reference to the description of the invention. It should be appreciated by those skilled in the art that the conception and the specific embodiment disclosed may be readily utilized as a basis for modifying or designing other structures for carrying out the same purposes of the present invention. It should also be realized by those skilled in the art that such equivalent constructions do not depart from the spirit and scope of the invention as set forth in the appended claims.

[0016] It is therefore, contemplated that the claims will cover any such modifications or embodiments that fall within the true scope of the invention.

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Application Data Sheet 37 CFR 1.76		Attorney Docket Number	GRTD60-35314
		Application Number	
Title of Invention	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS		
The application data sheet is part of the provisional or nonprovisional application for which it is being submitted. The following form contains the bibliographic data arranged in a format specified by the United States Patent and Trademark Office as outlined in 37 CFR 1.76. This document may be completed electronically and submitted to the Office in electronic format using the Electronic Filing System (EFS) or the document may be printed and included in a paper filed application.			

Secrecy Order 37 CFR 5.2:

☐	Portions or all of the application associated with this Application Data Sheet may fall under a Secrecy Order pursuant to 37 CFR 5.2 (Paper filers only. Applications that fall under Secrecy Order may not be filed electronically.)
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Inventor Information:

Inventor	1				Remove	
Legal Name						
Prefix	Given Name	Middle Name	Family Name	Suffix		
	G.R. MOHAN		RAO			
Residence Information (Select One) • US Residency Non US Residency Active US Military Service						
City	ALLEN	State/Province	TX	Country of Residence	US	
Mailing Address of Inventor:						
Address 1	1611 WILLINGHAM DRIVE					
Address 2						
City	ALLEN	State/Province	TX			
Postal Code	75013	Country	US			
All Inventors Must Be Listed - Additional Inventor Information blocks may be generated within this form by selecting the Add button.						

Correspondence Information:

Enter either Customer Number or complete the Correspondence Information section below. For further information see 37 CFR 1.33(a).	
☐ An Address is being provided for the correspondence information of this application.	
Customer Number	25883
Email Address	Add Email Remove Email

Application Information:

Title of the Invention	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS		
Attorney Docket Number	GRTD60-35314	Small Entity Status Claimed	☐
Application Type	Nonprovisional		
Subject Matter	Utility		
Total Number of Drawing Sheets (if any)		Suggested Figure for Publication (if any)	

Application Data Sheet 37 CFR 1.76		Attorney Docket Number	GRTD60-35314
		Application Number	
Title of Invention	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS		

Filing By Reference:

Only complete this section when filing an application by reference under 35 U.S.C. 111(c) and 37 CFR 1.57(a). Do not complete this section if application papers including a specification and any drawings are being filed. Any domestic benefit or foreign priority information must be provided in the appropriate section(s) below (i.e., "Domestic Benefit/National Stage Information" and "Foreign Priority Information").

For the purposes of a filing date under 37 CFR 1.53(b), the description and any drawings of the present application are replaced by this reference to the previously filed application, subject to conditions and requirements of 37 CFR 1.57(a).

Application number of the previously filed application	Filing date (YYYY-MM-DD)	Intellectual Property Authority or Country

Publication Information:

☐ Request Early Publication (Fee required at time of Request 37 CFR 1.219)

☐ **Request Not to Publish.** I hereby request that the attached application not be published under 35 U.S.C. 122(b) and certify that the invention disclosed in the attached application **has not and will not be** the subject of an application filed in another country, or under a multilateral international agreement, that requires publication at eighteen months after filing.

Representative Information:

Representative information should be provided for all practitioners having a power of attorney in the application. Providing this information in the Application Data Sheet does not constitute a power of attorney in the application (see 37 CFR 1.32). Either enter Customer Number or complete the Representative Name section below. If both sections are completed the customer Number will be used for the Representative Information during processing.

Please Select One:	☒ Customer Number	☐ US Patent Practitioner	☐ Limited Recognition (37 CFR 11.9)
Customer Number	25883		

Domestic Benefit/National Stage Information:

This section allows for the applicant to either claim benefit under 35 U.S.C. 119(e), 120, 121, 365(c), or 386(c) or indicate National Stage entry from a PCT application. Providing benefit claim information in the Application Data Sheet constitutes the specific reference required by 35 U.S.C. 119(e) or 120, and 37 CFR 1.78.

When referring to the current application, please leave the "Application Number" field blank.

Prior Application Status	Pending	Remove	
Application Number	Continuity Type	Prior Application Number	Filing or 371(c) Date (YYYY-MM-DD)
	Continuation of	16947294	2020-07-27

Application Data Sheet 37 CFR 1.76		Attorney Docket Number		GRTD60-35314	
		Application Number			
Title of Invention		SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS			

Prior Application Status		Patented		Remove	
Application Number	Continuity Type	Prior Application Number	Filing Date (YYYY-MM-DD)	Patent Number	Issue Date (YYYY-MM-DD)
16947294	Continuation of	16717950	2019-12-17	10734481	2020-08-04
Prior Application Status		Patented		Remove	
Application Number	Continuity Type	Prior Application Number	Filing Date (YYYY-MM-DD)	Patent Number	Issue Date (YYYY-MM-DD)
16717950	Continuation of	15590282	2017-05-09	10510842	2019-12-17
Prior Application Status		Patented		Remove	
Application Number	Continuity Type	Prior Application Number	Filing Date (YYYY-MM-DD)	Patent Number	Issue Date (YYYY-MM-DD)
15590282	Continuation of	14931636	2015-11-03	9647070	2017-05-09
Prior Application Status		Patented		Remove	
Application Number	Continuity Type	Prior Application Number	Filing Date (YYYY-MM-DD)	Patent Number	Issue Date (YYYY-MM-DD)
14931636	Continuation of	14515584	2014-10-16	9190502	2015-11-17
Prior Application Status		Abandoned		Remove	
Application Number	Continuity Type	Prior Application Number	Filing or 371(c) Date (YYYY-MM-DD)		
14515584	Continuation of	13854319	2013-04-01		
Prior Application Status		Patented		Remove	
Application Number	Continuity Type	Prior Application Number	Filing Date (YYYY-MM-DD)	Patent Number	Issue Date (YYYY-MM-DD)
13854319	Continuation of	11622496	2007-01-12	8421195	2013-04-16
Prior Application Status		Abandoned		Remove	
Application Number	Continuity Type	Prior Application Number	Filing or 371(c) Date (YYYY-MM-DD)		
11622496	Division of	10934915	2004-09-03		
Additional Domestic Benefit/National Stage Data may be generated within this form by selecting the Add button. Add					

Foreign Priority Information:

This section allows for the applicant to claim priority to a foreign application. Providing this information in the application data sheet constitutes the claim for priority as required by 35 U.S.C. 119(b) and 37 CFR 1.55. When priority is claimed to a foreign application that is eligible for retrieval under the priority document exchange program (PDX)ⁱ the information will be used by the Office to automatically attempt retrieval pursuant to 37 CFR 1.55(i)(1) and (2). Under the PDX program, applicant bears the ultimate responsibility for ensuring that a copy of the foreign application is received by the Office from the participating foreign intellectual property office, or a certified copy of the foreign priority application is filed, within the time period specified in 37 CFR 1.55(g)(1).

Application Data Sheet 37 CFR 1.76		Attorney Docket Number	GRTD60-35314
		Application Number	
Title of Invention	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS		

			Remove
Application Number	Country ⁱ	Filing Date (YYYY-MM-DD)	Access Code ^j (if applicable)
Additional Foreign Priority Data may be generated within this form by selecting the Add button.			Add

Statement under 37 CFR 1.55 or 1.78 for AIA (First Inventor to File) Transition Applications

☐ This application (1) claims priority to or the benefit of an application filed before March 16, 2013 and (2) also contains, or contained at any time, a claim to a claimed invention that has an effective filing date on or after March 16, 2013. NOTE: By providing this statement under 37 CFR 1.55 or 1.78, this application, with a filing date on or after March 16, 2013, will be examined under the first inventor to file provisions of the AIA.

Application Data Sheet 37 CFR 1.76		Attorney Docket Number	GRTD60-35314
		Application Number	
Title of Invention	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS		

Authorization or Opt-Out of Authorization to Permit Access:

When this Application Data Sheet is properly signed and filed with the application, applicant has provided written authority to permit a participating foreign intellectual property (IP) office access to the instant application-as-filed (see paragraph A in subsection 1 below) and the European Patent Office (EPO) access to any search results from the instant application (see paragraph B in subsection 1 below).

Should applicant choose not to provide an authorization identified in subsection 1 below, applicant **must opt-out** of the authorization by checking the corresponding box A or B or both in subsection 2 below.

NOTE: This section of the Application Data Sheet is **ONLY** reviewed and processed with the **INITIAL** filing of an application. After the initial filing of an application, an Application Data Sheet cannot be used to provide or rescind authorization for access by a foreign IP office(s). Instead, Form PTO/SB/39 or PTO/SB/69 must be used as appropriate.

1. Authorization to Permit Access by a Foreign Intellectual Property Office(s)

A. Priority Document Exchange (PDX) - Unless box A in subsection 2 (opt-out of authorization) is checked, the undersigned hereby **grants the USPTO authority** to provide the European Patent Office (EPO), the Japan Patent Office (JPO), the Korean Intellectual Property Office (KIPO), the State Intellectual Property Office of the People's Republic of China (SIPO), the World Intellectual Property Organization (WIPO), and any other foreign intellectual property office participating with the USPTO in a bilateral or multilateral priority document exchange agreement in which a foreign application claiming priority to the instant patent application is filed, access to: (1) the instant patent application-as-filed and its related bibliographic data, (2) any foreign or domestic application to which priority or benefit is claimed by the instant application and its related bibliographic data, and (3) the date of filing of this Authorization. See 37 CFR 1.14(h)(1).

B. Search Results from U.S. Application to EPO - Unless box B in subsection 2 (opt-out of authorization) is checked, the undersigned hereby **grants the USPTO authority** to provide the EPO access to the bibliographic data and search results from the instant patent application when a European patent application claiming priority to the instant patent application is filed. See 37 CFR 1.14(h)(2).

The applicant is reminded that the EPO's Rule 141(1) EPC (European Patent Convention) requires applicants to submit a copy of search results from the instant application without delay in a European patent application that claims priority to the instant application.

2. Opt-Out of Authorizations to Permit Access by a Foreign Intellectual Property Office(s)

☐ A. Applicant **DOES NOT** authorize the USPTO to permit a participating foreign IP office access to the instant application-as-filed. If this box is checked, the USPTO will not be providing a participating foreign IP office with any documents and information identified in subsection 1A above.

☐ B. Applicant **DOES NOT** authorize the USPTO to transmit to the EPO any search results from the instant patent application. If this box is checked, the USPTO will not be providing the EPO with search results from the instant application.

NOTE: Once the application has published or is otherwise publicly available, the USPTO may provide access to the application in accordance with 37 CFR 1.14.

Application Data Sheet 37 CFR 1.76		Attorney Docket Number	GRTD60-35314
		Application Number	
Title of Invention	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS		

Applicant Information:

Providing assignment information in this section does not substitute for compliance with any requirement of part 3 of Title 37 of CFR to have an assignment recorded by the Office.

Applicant	1	Remove
If the applicant is the inventor (or the remaining joint inventor or inventors under 37 CFR 1.45), this section should not be completed. The information to be provided in this section is the name and address of the legal representative who is the applicant under 37 CFR 1.43; or the name and address of the assignee, person to whom the inventor is under an obligation to assign the invention, or person who otherwise shows sufficient proprietary interest in the matter who is the applicant under 37 CFR 1.46. If the applicant is an applicant under 37 CFR 1.46 (assignee, person to whom the inventor is obligated to assign, or person who otherwise shows sufficient proprietary interest) together with one or more joint inventors, then the joint inventor or inventors who are also the applicant should be identified in this section. Clear		
☒ Assignee	Legal Representative under 35 U.S.C. 117	Joint Inventor
Person to whom the inventor is obligated to assign.		Person who shows sufficient proprietary interest
If applicant is the legal representative, indicate the authority to file the patent application, the inventor is:		
Name of the Deceased or Legally Incapacitated Inventor:		
If the Applicant is an Organization check here. ☒		
Organization Name	GREENTHREAD, LLC	
Mailing Address Information For Applicant:		
Address 1	4544 Harrys Lane	
Address 2		
City	Dallas	State/Province TX
Country	US	Postal Code 75229
Phone Number		Fax Number
Email Address		
Additional Applicant Data may be generated within this form by selecting the Add button. Add		

Assignee Information including Non-Applicant Assignee Information:

Providing assignment information in this section does not substitute for compliance with any requirement of part 3 of Title 37 of CFR to have an assignment recorded by the Office.

Application Data Sheet 37 CFR 1.76		Attorney Docket Number	GRTD60-35314
		Application Number	
Title of Invention	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS		

Assignee	1			
Complete this section if assignee information, including non-applicant assignee information, is desired to be included on the patent application publication. An assignee-applicant identified in the "Applicant Information" section will appear on the patent application publication as an applicant. For an assignee-applicant, complete this section only if identification as an assignee is also desired on the patent application publication.				
				Remove
If the Assignee or Non-Applicant Assignee is an Organization check here.				☐
Prefix	Given Name	Middle Name	Family Name	Suffix
Mailing Address Information For Assignee including Non-Applicant Assignee:				
Address 1				
Address 2				
City		State/Province		
Country ⁱ		Postal Code		
Phone Number		Fax Number		
Email Address				
Additional Assignee or Non-Applicant Assignee Data may be generated within this form by selecting the Add button.				Add

Signature:

NOTE: This Application Data Sheet must be signed in accordance with 37 CFR 1.33(b). However, if this Application Data Sheet is submitted with the **INITIAL** filing of the application and either box A or B is not checked in subsection 2 of the "Authorization or Opt-Out of Authorization to Permit Access" section, then this form must also be signed in accordance with 37 CFR 1.14(c).

This Application Data Sheet **must** be signed by a patent practitioner if one or more of the applicants is a **juristic entity** (e.g., corporation or association). If the applicant is two or more joint inventors, this form must be signed by a patent practitioner, **all** joint inventors who are the applicant, or one or more joint inventor-applicants who have been given power of attorney (e.g., see USPTO Form PTO/AIA/81) on behalf of **all** joint inventor-applicants.

See 37 CFR 1.4(d) for the manner of making signatures and certifications.

Signature	/Gregory M. Howison, Reg. #30646/		Date (YYYY-MM-DD)	2021-07-09
First Name	Gregory	Last Name	Howison	Registration Number
				30646
Additional Signature may be generated within this form by selecting the Add button.				Add

Application Data Sheet 37 CFR 1.76		Attorney Docket Number	GRTD60-35314
		Application Number	
Title of Invention	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS		

This collection of information is required by 37 CFR 1.76. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 23 minutes to complete, including gathering, preparing, and submitting the completed application data sheet form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. **SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.**

Privacy Act Statement

The Privacy Act of 1974 (P.L. 93-579) requires that you be given certain information in connection with your submission of the attached form related to a patent application or patent. Accordingly, pursuant to the requirements of the Act, please be advised that: (1) the general authority for the collection of this information is 35 U.S.C. 2(b)(2); (2) furnishing of the information solicited is voluntary; and (3) the principal purpose for which the information is used by the U.S. Patent and Trademark Office is to process and/or examine your submission related to a patent application or patent. If you do not furnish the requested information, the U.S. Patent and Trademark Office may not be able to process and/or examine your submission, which may result in termination of proceedings or abandonment of the application or expiration of the patent.

The information provided by you in this form will be subject to the following routine uses:

1. The information on this form will be treated confidentially to the extent allowed under the Freedom of Information Act (5 U.S.C. 552) and the Privacy Act (5 U.S.C. 552a). Records from this system of records may be disclosed to the Department of Justice to determine whether the Freedom of Information Act requires disclosure of these records.
2. A record from this system of records may be disclosed, as a routine use, in the course of presenting evidence to a court, magistrate, or administrative tribunal, including disclosures to opposing counsel in the course of settlement negotiations.
3. A record in this system of records may be disclosed, as a routine use, to a Member of Congress submitting a request involving an individual, to whom the record pertains, when the individual has requested assistance from the Member with respect to the subject matter of the record.
4. A record in this system of records may be disclosed, as a routine use, to a contractor of the Agency having need for the information in order to perform a contract. Recipients of information shall be required to comply with the requirements of the Privacy Act of 1974, as amended, pursuant to 5 U.S.C. 552a(m).
5. A record related to an International Application filed under the Patent Cooperation Treaty in this system of records may be disclosed, as a routine use, to the International Bureau of the World Intellectual Property Organization, pursuant to the Patent Cooperation Treaty.
6. A record in this system of records may be disclosed, as a routine use, to another federal agency for purposes of National Security review (35 U.S.C. 181) and for review pursuant to the Atomic Energy Act (42 U.S.C. 218(c)).
7. A record from this system of records may be disclosed, as a routine use, to the Administrator, General Services, or his/her designee, during an inspection of records conducted by GSA as part of that agency's responsibility to recommend improvements in records management practices and programs, under authority of 44 U.S.C. 2904 and 2906. Such disclosure shall be made in accordance with the GSA regulations governing inspection of records for this purpose, and any other relevant (i.e., GSA or Commerce) directive. Such disclosure shall not be used to make determinations about individuals.
8. A record from this system of records may be disclosed, as a routine use, to the public after either publication of the application pursuant to 35 U.S.C. 122(b) or issuance of a patent pursuant to 35 U.S.C. 151. Further, a record may be disclosed, subject to the limitations of 37 CFR 1.14, as a routine use, to the public if the record was filed in an application which became abandoned or in which the proceedings were terminated and which application is referenced by either a published application, an application open to public inspections or an issued patent.
9. A record from this system of records may be disclosed, as a routine use, to a Federal, State, or local law enforcement agency, if the USPTO becomes aware of a violation or potential violation of law or regulation.

Electronic Patent Application Fee Transmittal

Application Number:

Filing Date:

Title of Invention:

SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS

First Named Inventor/Applicant Name:

G. R. Mohan Rao

Filer:

Gregory Michael Howison/Joselyn Rodriguez

Attorney Docket Number:

GRTD60-35314

Filed as Large Entity

Filing Fees for Track I Prioritized Examination - Nonprovisional Application under 35 USC 111(a)

Description	Fee Code	Quantity	Amount	Sub-Total in USD(\$)
Basic Filing:				
UTILITY APPLICATION FILING	1011	1	320	320
UTILITY SEARCH FEE	1111	1	700	700
UTILITY EXAMINATION FEE	1311	1	800	800
REQUEST FOR PRIORITIZED EXAMINATION	1817	1	4200	4200

Pages:

Claims:

CLAIMS IN EXCESS OF 20	1202	10	100	1000
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Miscellaneous-Filing:

Description	Fee Code	Quantity	Amount	Sub-Total in USD(\$)
PUBL. FEE- EARLY, VOLUNTARY, OR NORMAL	1504	1	0	0
PROCESSING FEE, EXCEPT PROV. APPLS.	1830	1	140	140
Petition:				
Patent-Appeals-and-Interference:				
Post-Allowance-and-Post-Issuance:				
Extension-of-Time:				
Miscellaneous:				
Total in USD (\$)				7160

Electronic Acknowledgement Receipt

EFS ID:	43208746
Application Number:	17371839
International Application Number:	
Confirmation Number:	2197
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS
First Named Inventor/Applicant Name:	G. R. Mohan Rao
Customer Number:	25883
Filer:	Gregory Michael Howison/Joselyn Rodriguez
Filer Authorized By:	Gregory Michael Howison
Attorney Docket Number:	GRTD60-35314
Receipt Date:	09-JUL-2021
Filing Date:	
Time Stamp:	15:54:57
Application Type:	Utility under 35 USC 111(a)

Payment information:

Submitted with Payment	yes
Payment Type	CARD
Payment was successfully received in RAM	\$7160
RAM confirmation Number	E202179F55414118
Deposit Account	500208
Authorized User	Joselyn Rodriguez

The Director of the USPTO is hereby authorized to charge indicated fees and credit any overpayment as follows:

37 CFR 1.16 (National application filing, search, and examination fees)

37 CFR 1.17 (Patent application and reexamination processing fees)

Dell Ex. 1002

Page 40

File Listing:

Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)
1	TrackOne Request	GRT35314TRACKONE.pdf	140549	no	2
			779d93c31db6608eb657b16f6f66853e26f30ffe		
Warnings:					
Information:					
2	Drawings-only black and white line drawings	GRT35314DWGS.pdf	3441256	no	10
			31b25c7e387f925f58cd58d1c08f8bd71bdaf80e		
Warnings:					
Information:					
3	Power of Attorney	GRT35314POAEXE.pdf	1583112	no	2
			08b2695aac1899d04843b5ffb8b114e330f0cdf3		
Warnings:					
Information:					
4	Oath or Declaration filed	GRT35314DECEXE.pdf	102924	no	1
			425aabcd457f692cf118f871fd294b201f2dee5f		
Warnings:					
Information:					
5		GRT35314CON.pdf	145967	yes	13
			34de3341512aa1ec1f11993602ac6ed6210a5b2e		
	Multipart Description/PDF files in .zip description				
	Document Description		Start	End	
	Abstract		13	13	
	Claims		9	12	
	Specification		1	8	
Dell Ex. 1002					

Warnings:					
Information:					
6	Application Data Sheet	GRT35314ADS.pdf	1874721	no	9
			78965d0da00b7db97d3f7430b8be76363c3fa998		
Warnings:					
Information:					
7	Fee Worksheet (SB06)	fee-info.pdf	41799	no	2
			2b3d674d035c0fbc0e3fa6592b303de43ff4633a		
Warnings:					
Information:					
Total Files Size (in bytes):			7330328		
This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503. <u>New Applications Under 35 U.S.C. 111</u> If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application. <u>National Stage of an International Application under 35 U.S.C. 371</u> If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course. <u>New International Application Filed with the USPTO as a Receiving Office</u> If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.					



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APPLICATION NUMBER	FILING OR 371(C) DATE	FIRST NAMED APPLICANT	ATTY. DOCKET NO./TITLE
17/371,839	07/09/2021	G.R. MOHAN RAO	GRTD60-35314

CONFIRMATION NO. 2197

FORMALITIES LETTER



25883
MUNCK WILSON MANDALA L.L.P
P.O. Drawer 800889
DALLAS, TX 75380

Date Mailed: 07/23/2021

NOTICE TO FILE CORRECTED APPLICATION PAPERS

Filing Date Granted

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/hnguyen/

PATENT APPLICATION FEE DETERMINATION RECORD Substitute for Form PTO-875						Application or Docket Number 17/371,839				
APPLICATION AS FILED - PART I										
(Column 1)		(Column 2)		SMALL ENTITY		OR OTHER THAN SMALL ENTITY				
FOR	NUMBER FILED	NUMBER EXTRA	RATE(\$)	FEE(\$)		RATE(\$)	FEE(\$)			
BASIC FEE (37 CFR 1.16(a), (b), or (c))	N/A	N/A	N/A			N/A	320			
SEARCH FEE (37 CFR 1.16(k), (l), or (m))	N/A	N/A	N/A			N/A	700			
EXAMINATION FEE (37 CFR 1.16(o), (p), or (q))	N/A	N/A	N/A			N/A	800			
TOTAL CLAIMS (37 CFR 1.16(j))	30 minus 20 =	*				x 100 =	1000			
INDEPENDENT CLAIMS (37 CFR 1.16(h))	2 minus 3 =	*				x 480 =	0.00			
APPLICATION SIZE FEE (37 CFR 1.16(s))	If the specification and drawings exceed 100 sheets of paper, the application size fee due is \$310 (\$155 for small entity) for each additional 50 sheets or fraction thereof. See 35 U.S.C. 41(a)(1)(G) and 37 CFR 1.16(s).						0.00			
MULTIPLE DEPENDENT CLAIM PRESENT (37 CFR 1.16(j))							0.00			
* If the difference in column 1 is less than zero, enter "0" in column 2.				TOTAL		TOTAL	2820			
APPLICATION AS AMENDED - PART II										
(Column 1)		(Column 2)		(Column 3)		SMALL ENTITY		OR OTHER THAN SMALL ENTITY		
AMENDMENT A		CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA	RATE(\$)	ADDITIONAL FEE(\$)		RATE(\$)	ADDITIONAL FEE(\$)
	Total (37 CFR 1.16(i))	*	Minus	**	=	x =			x =	
	Independent (37 CFR 1.16(h))	*	Minus	***	=	x =			x =	
	Application Size Fee (37 CFR 1.16(s))									
	FIRST PRESENTATION OF MULTIPLE DEPENDENT CLAIM (37 CFR 1.16(j))									
						TOTAL ADD'L FEE			TOTAL ADD'L FEE	
AMENDMENT B		CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA	RATE(\$)	ADDITIONAL FEE(\$)		RATE(\$)	ADDITIONAL FEE(\$)
	Total (37 CFR 1.16(i))	*	Minus	**	=	x =			x =	
	Independent (37 CFR 1.16(h))	*	Minus	***	=	x =			x =	
	Application Size Fee (37 CFR 1.16(s))									
	FIRST PRESENTATION OF MULTIPLE DEPENDENT CLAIM (37 CFR 1.16(j))									
						TOTAL ADD'L FEE			TOTAL ADD'L FEE	
* If the entry in column 1 is less than the entry in column 2, write "0" in column 3. ** If the "Highest Number Previously Paid For" IN THIS SPACE is less than 20, enter "20". *** If the "Highest Number Previously Paid For" IN THIS SPACE is less than 3, enter "3". The "Highest Number Previously Paid For" (Total or Independent) is the highest found in the appropriate box in column 1.										



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APPLICATION NUMBER	FILING or 371(c) DATE	GRP ART UNIT	FIL FEE REC'D	ATTY. DOCKET NO	TOT CLAIMS	IND CLAIMS
17/371,839	07/09/2021	2812	2820	GRTD60-35314	30	2

CONFIRMATION NO. 2197

FILING RECEIPT

25883
MUNCK WILSON MANDALA L.L.P.
P.O. Drawer 800889
DALLAS, TX 75380



Date Mailed: 07/23/2021

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Inventor(s)

G.R. MOHAN RAO, ALLEN, TX;

Applicant(s)

GREENTHREAD, LLC, Dallas, TX;

Power of Attorney: The patent practitioners associated with Customer Number 25883

Domestic Priority data as claimed by applicant

This application is a CON of 16/947,294 07/27/2020
which is a CON of 16/717,950 12/17/2019 PAT 10734481
which is a CON of 15/590,282 05/09/2017 PAT 10510842
which is a CON of 14/931,636 11/03/2015 PAT 9647070
which is a CON of 14/515,584 10/16/2014 PAT 9190502
which is a CON of 13/854,319 04/01/2013 ABN
which is a CON of 11/622,496 01/12/2007 PAT 8421195
which is a DIV of 10/934,915 09/03/2004 ABN

Foreign Applications for which priority is claimed (You may be eligible to benefit from the **Patent Prosecution Highway** program at the USPTO. Please see <http://www.uspto.gov> for more information.) - None.

Foreign application information must be provided in an Application Data Sheet in order to constitute a claim to foreign priority. See 37 CFR 1.55 and 1.76.

Permission to Access Application via Priority Document Exchange: Yes

Permission to Access Search Results: Yes

Applicant may provide or rescind an authorization for access using Form PTO/SB/39 or Form PTO/SB/69 as appropriate.

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The country code and number of your priority application, to be used for filing abroad under the Paris Convention, is **US 17/371,839**

Projected Publication Date: To Be Determined - pending completion of Corrected Papers

Non-Publication Request: No

Early Publication Request: No

Title

SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS

Preliminary Class

438

Statement under 37 CFR 1.55 or 1.78 for AIA (First Inventor to File) Transition Applications: No

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Since the rights granted by a U.S. patent extend only throughout the territory of the United States and have no effect in a foreign country, an inventor who wishes patent protection in another country must apply for a patent in a specific country or in regional patent offices. Applicants may wish to consider the filing of an international application under the Patent Cooperation Treaty (PCT). An international (PCT) application generally has the same effect as a regular national patent application in each PCT-member country. The PCT process **simplifies** the filing of patent applications on the same invention in member countries, but **does not result** in a grant of "an international patent" and does not eliminate the need of applicants to file additional documents and fees in countries where patent protection is desired.

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page 2 of 4

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: G.R. Mohan RAO
Serial No.: 17/371,839
Confirmation No.: 2197
Filed: July 9, 2021
Group: 2812
Examiner: To be assigned
For: SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS

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Commissioner for Patents
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Alexandria, VA 22313-1450

Dear Sir:

RESPONSE TO NOTICE TO FILE CORRECTED APPLICATION PAPERS

In response to the Notice to File Corrected Application Papers dated July 23, 2021, the Applicant submits replacement Drawings marked "Replacement Sheets."

Please charge any additional fees or deficiencies in fees or credit any overpayment to Deposit Account No. 50-0208/GRTD60-35314.

Respectfully submitted,
MUNCK WILSON MANDALA, LLP
Attorneys for Applicant(s)

/Gregory M. Howison, Reg. #30,646/

Gregory M. Howison
Registration No. 30,646

GMH/als
P.O. Drawer 800889
Dallas, Texas 75380
Tel: 972-628-3600
Fax: 972-628-3616
August 9, 2021

RESPONSE TO NOTICE TO FILE CORRECTED APPLICATION PAPERS

SN: 17/371,839
Atty. Dkt. No. GRTD60-35314



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APPLICATION NUMBER	FILING OR 371(C) DATE	FIRST NAMED APPLICANT	ATTY. DOCKET NO./TITLE
17/371,839	07/09/2021	G.R. MOHAN RAO	GRTD60-35314

CONFIRMATION NO. 2197

FORMALITIES LETTER



25883
MUNCK WILSON MANDALA L.L.P
P.O. Drawer 800889
DALLAS, TX 75380

Date Mailed: 07/23/2021

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- Replacement drawings in compliance with 37 CFR 1.84 and 37 CFR 1.121(d) are required. The drawings submitted are not acceptable because:
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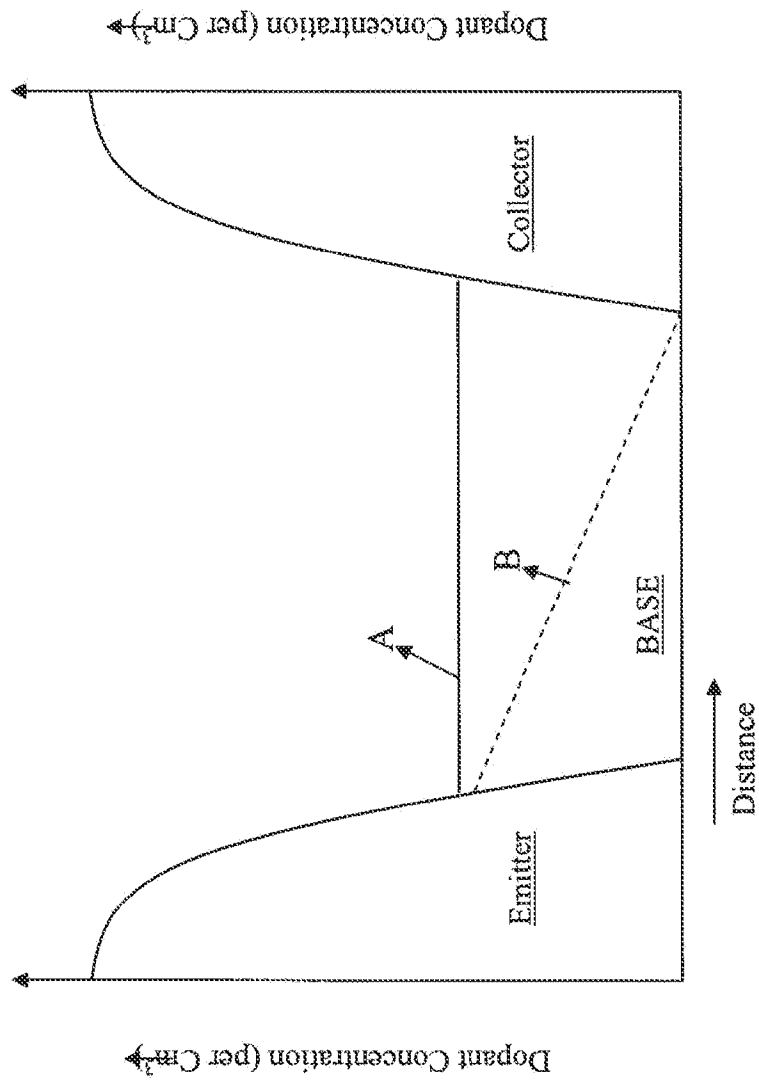
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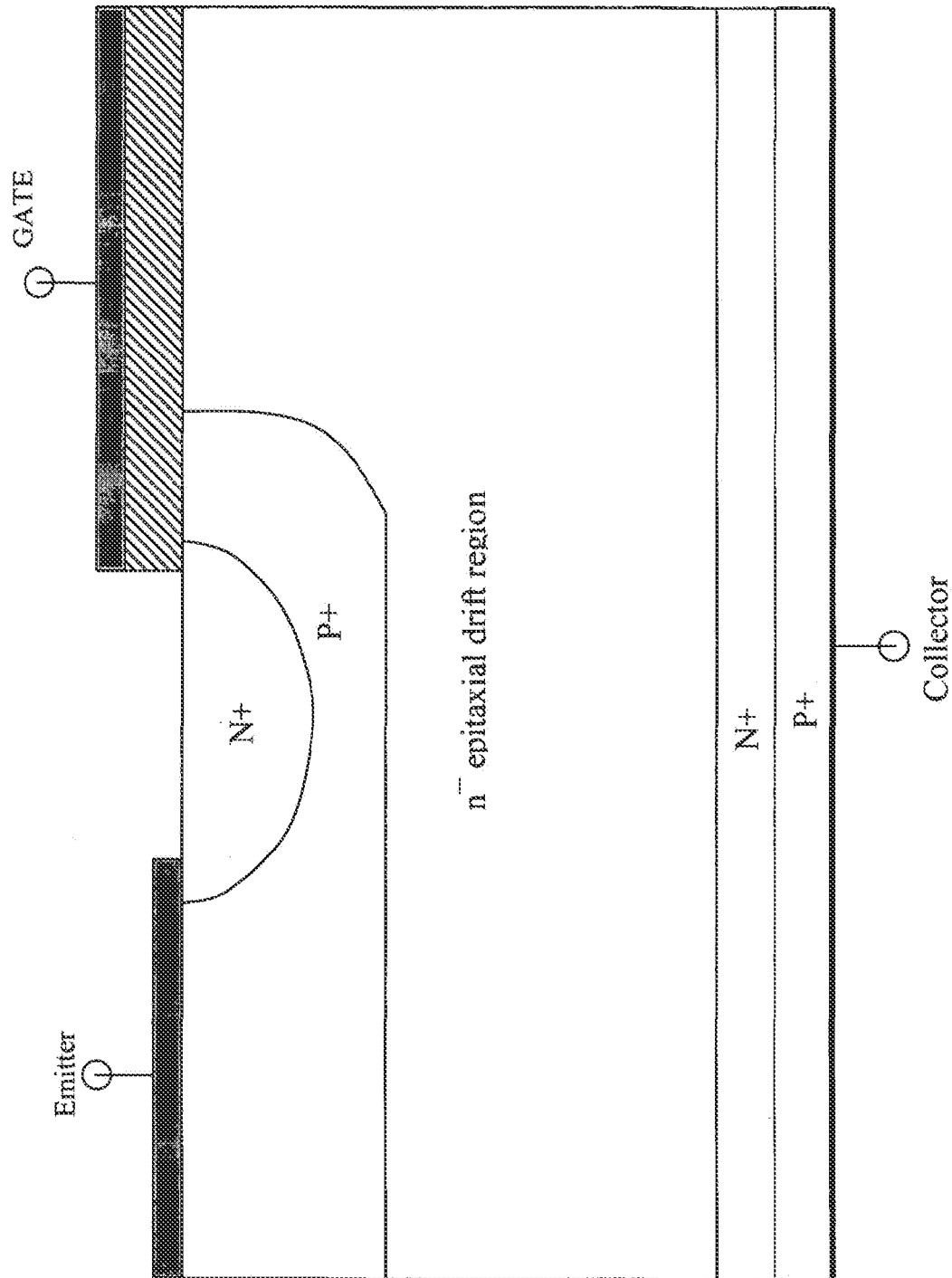
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/hnguyen/

Figure 1 Prior Art

FIGURE 2 Prior art

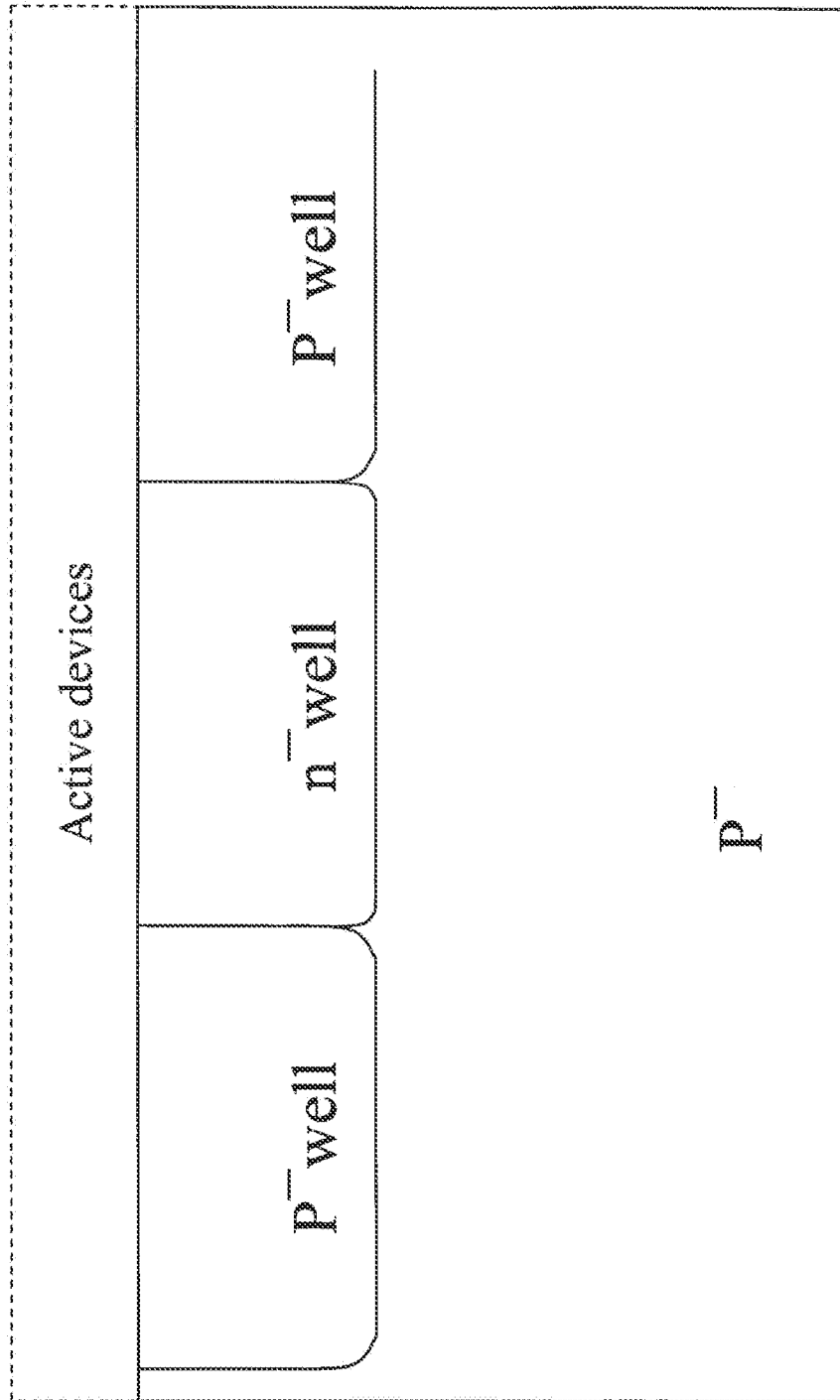


FIGURE 3A Prior art

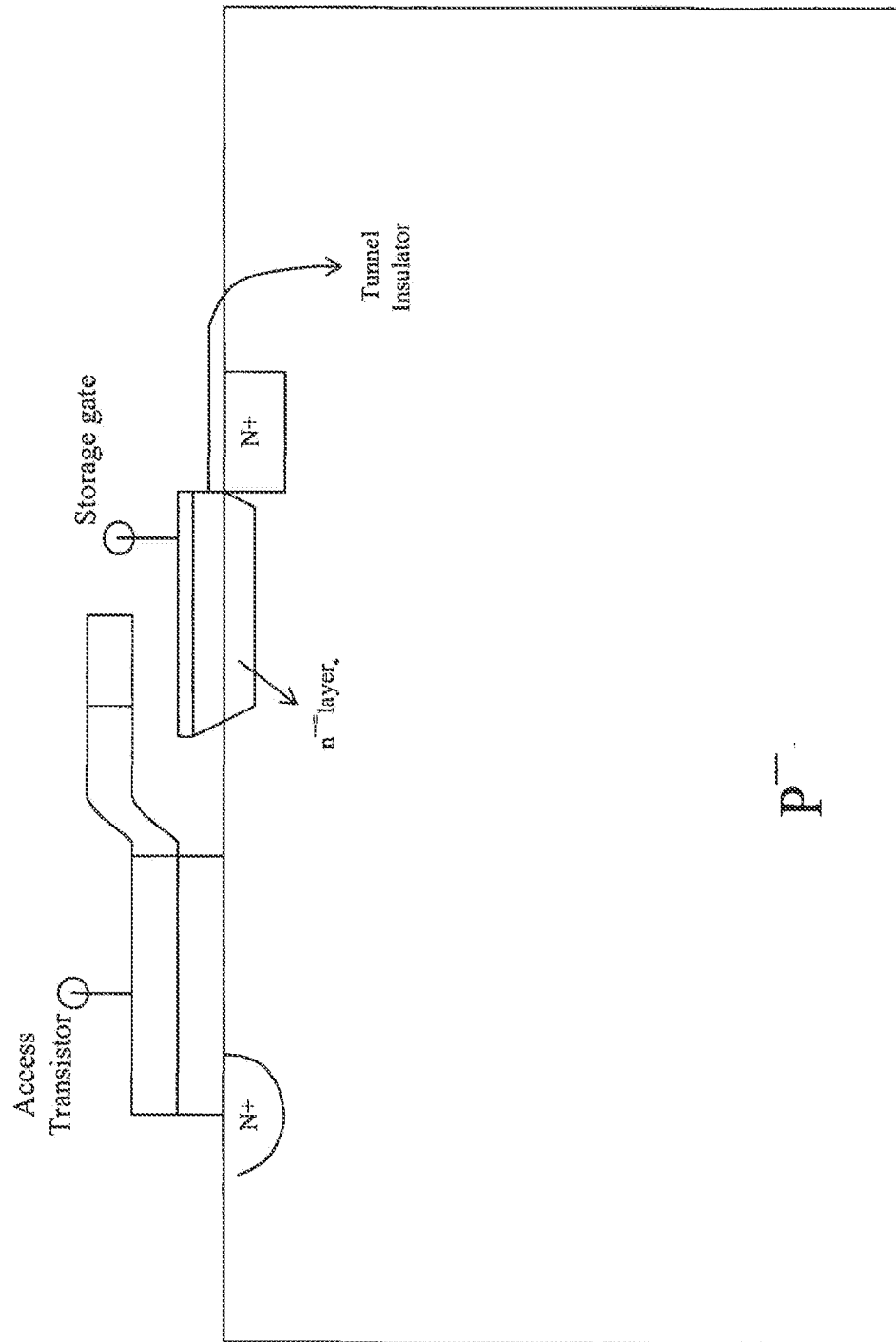
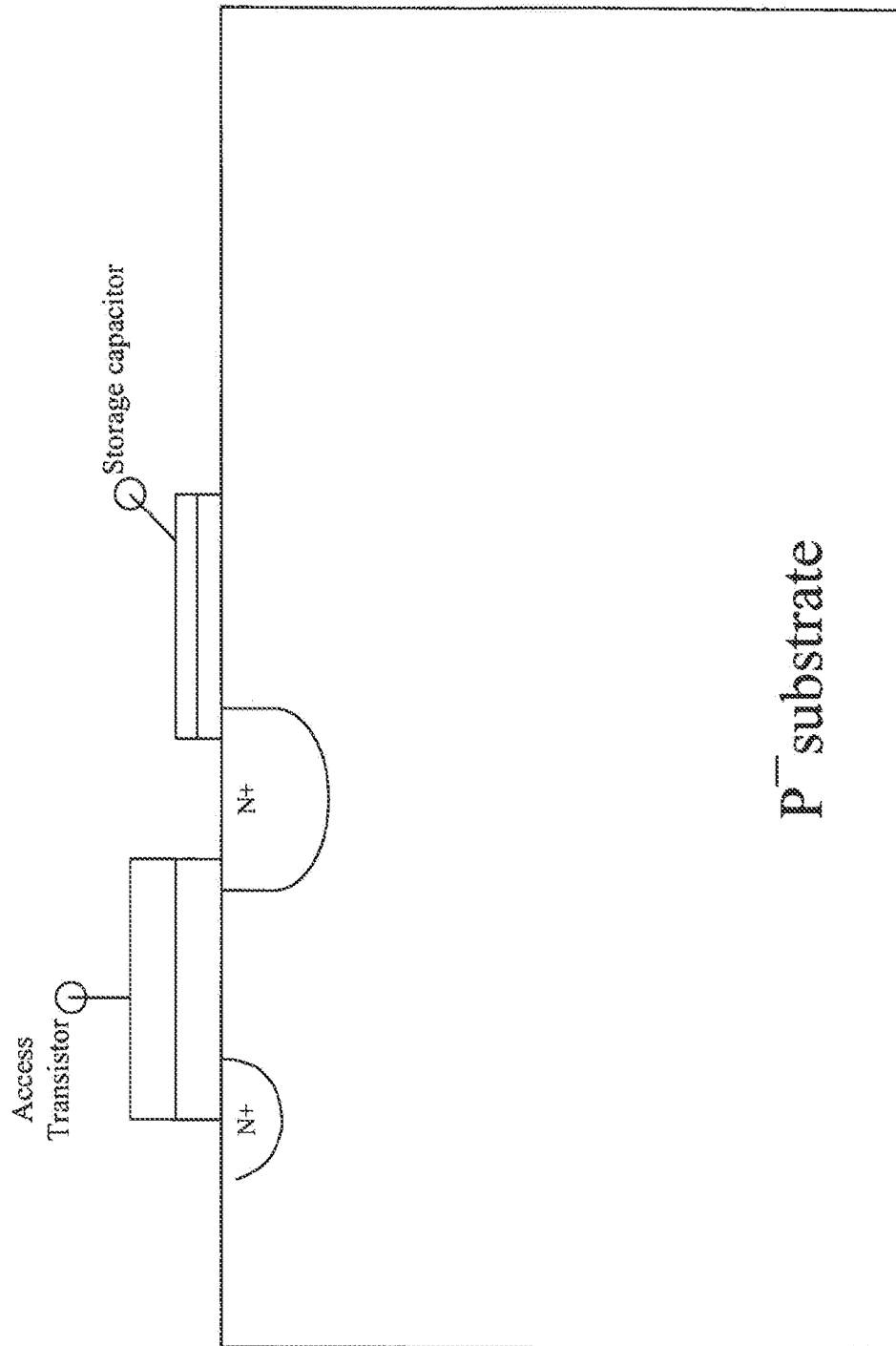
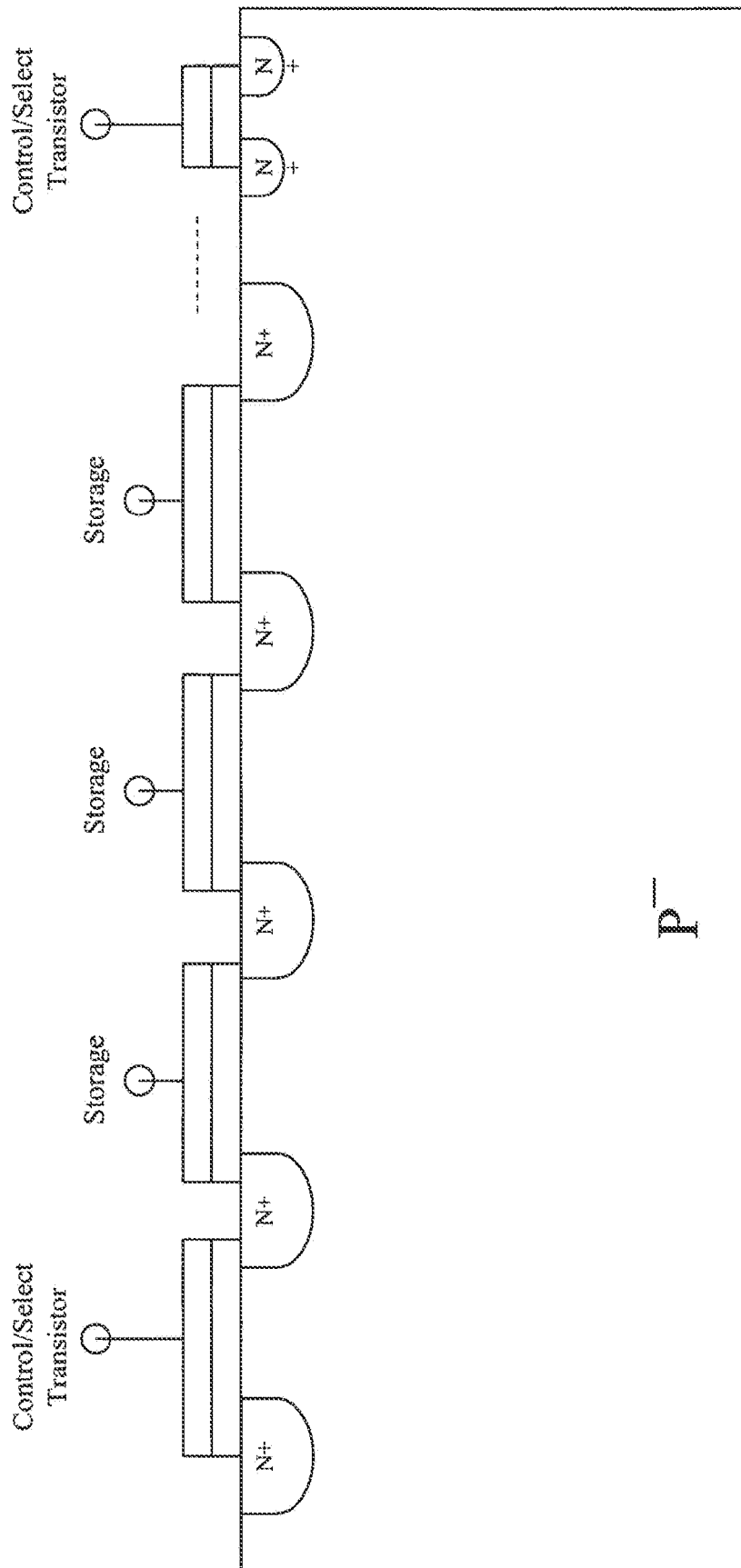


FIGURE 3B Prior art

FIGURE 3C Prior art

FIGURE 3D Prior art

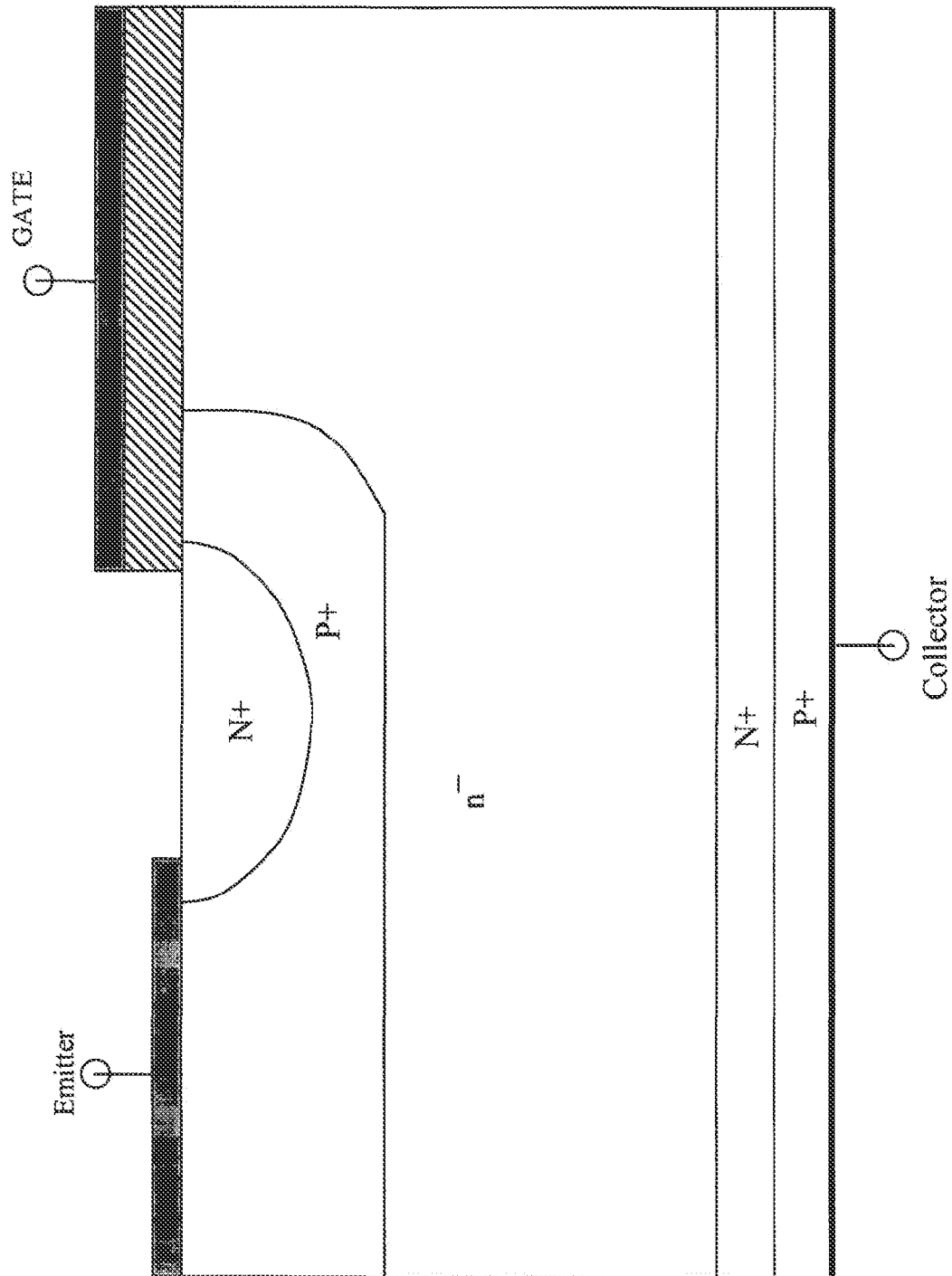
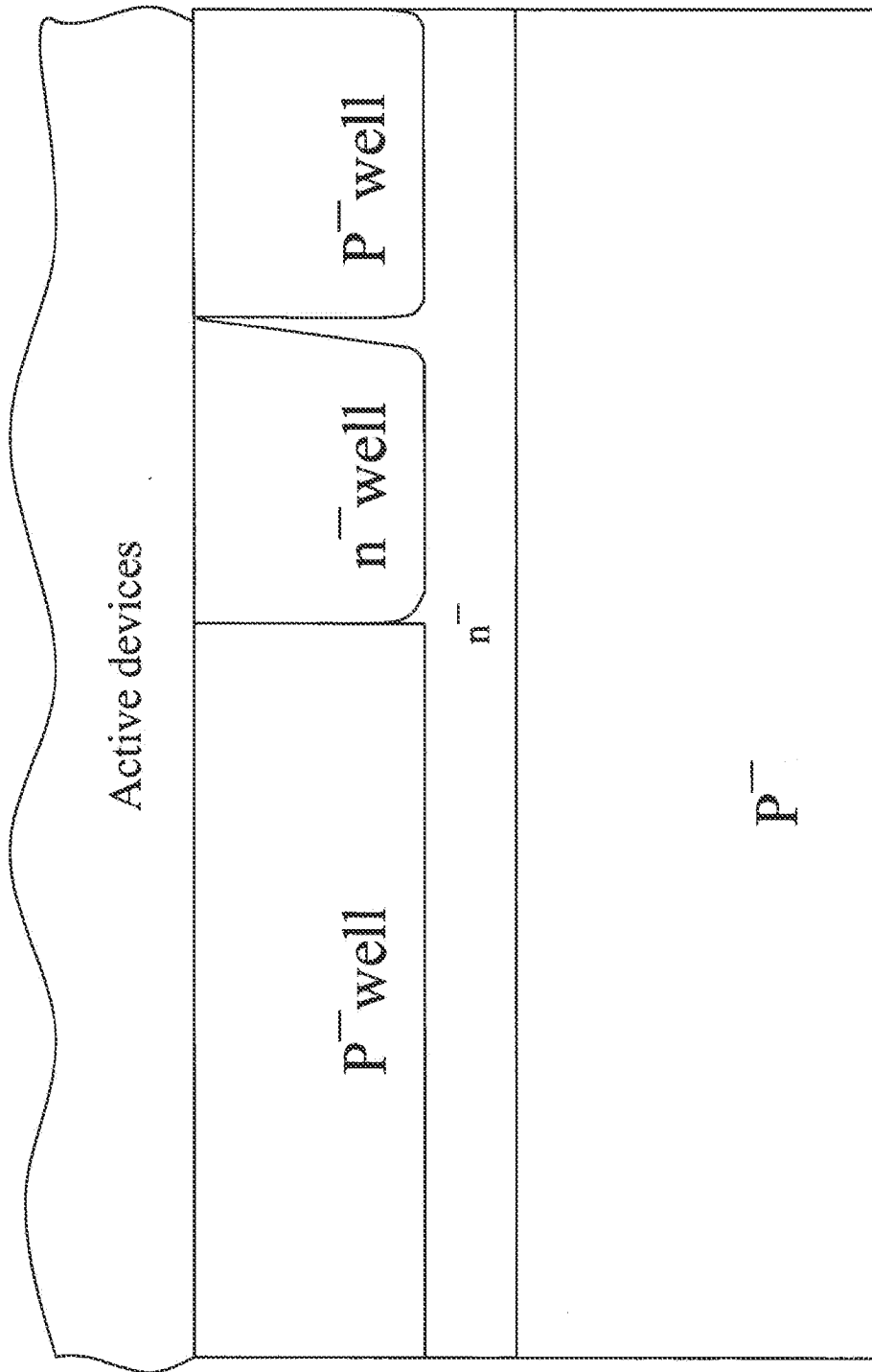


FIGURE 4

FIGURE 5A

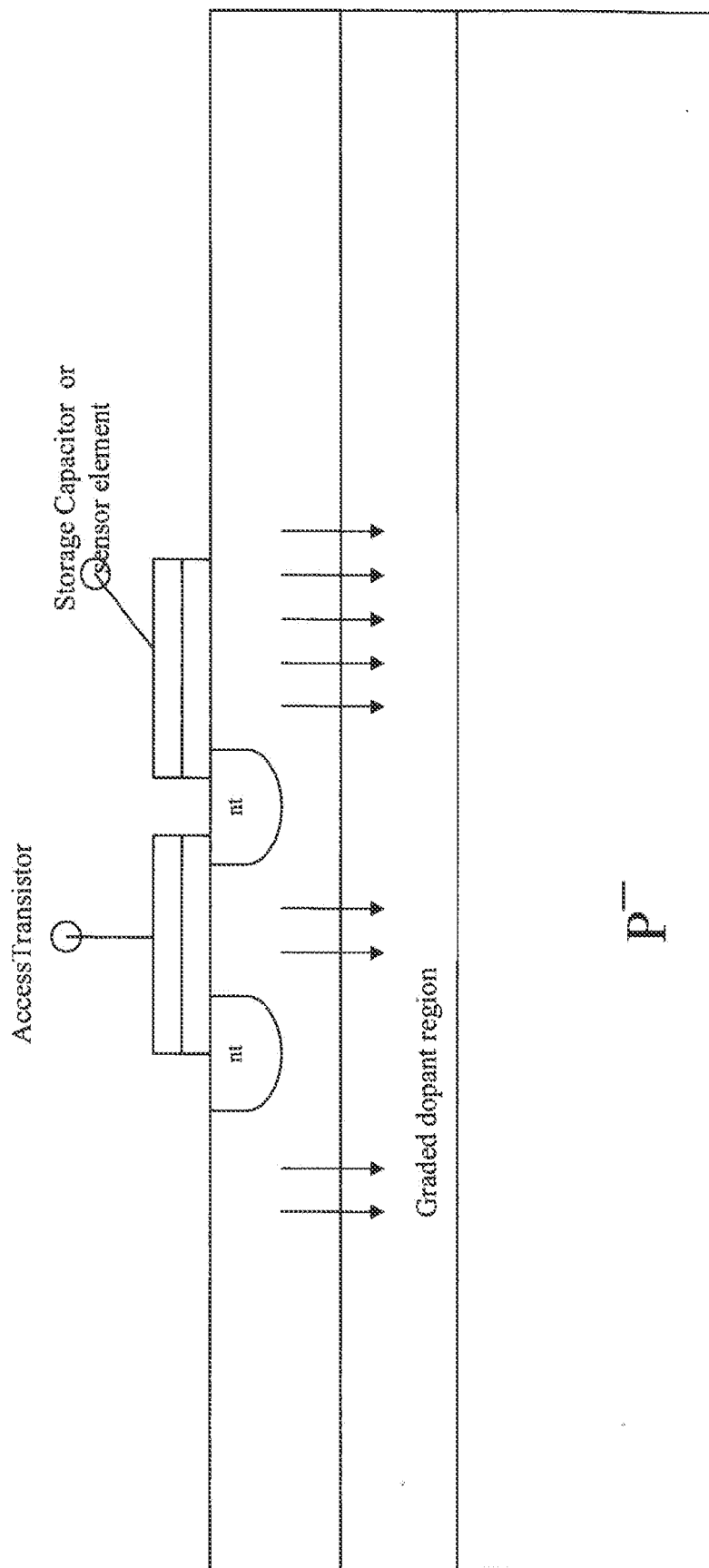


FIGURE 5B

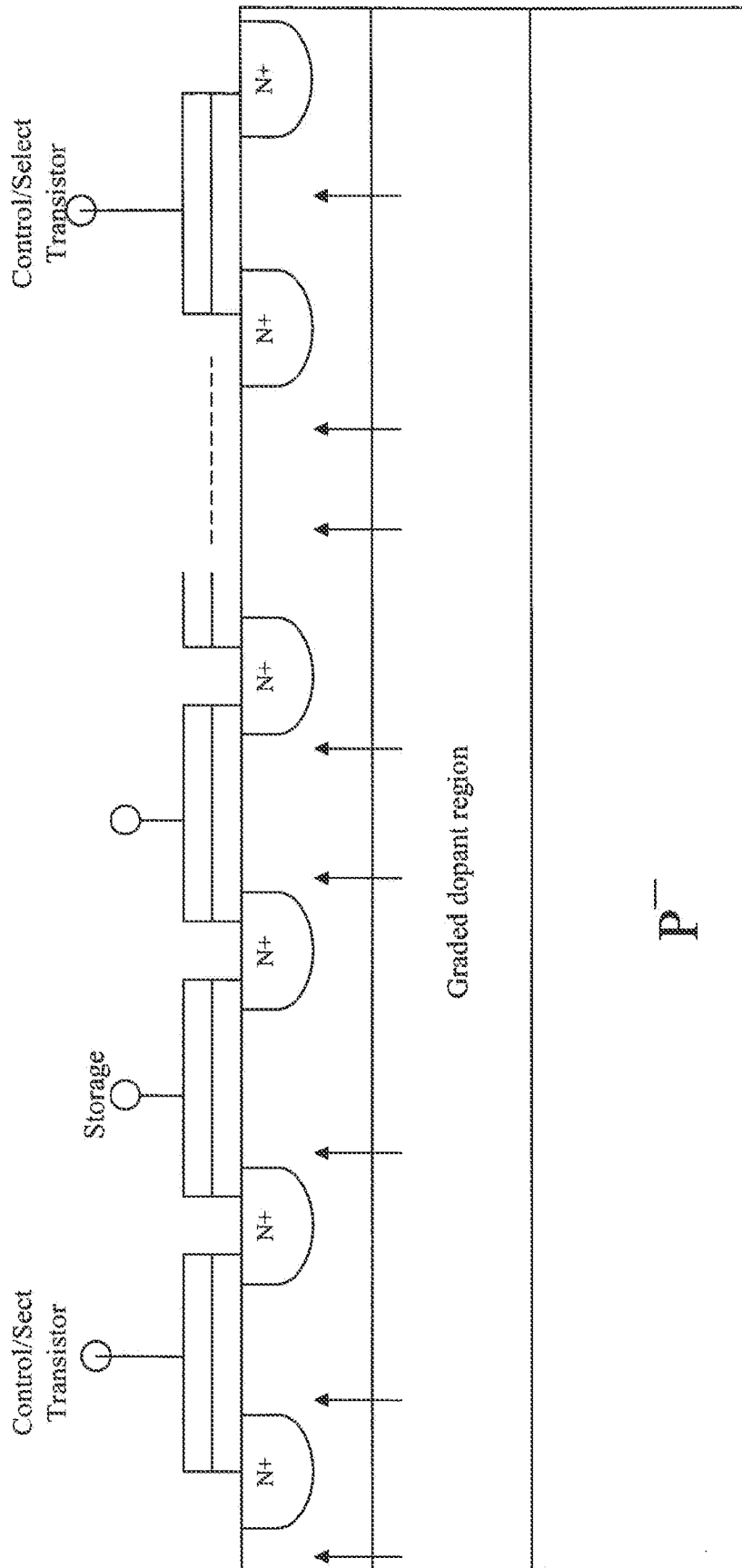


FIGURE 5C

Electronic Acknowledgement Receipt

EFS ID:	43455028
Application Number:	17371839
International Application Number:	
Confirmation Number:	2197
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS
First Named Inventor/Applicant Name:	G.R. MOHAN RAO
Customer Number:	25883
Filer:	Gregory Michael Howison
Filer Authorized By:	
Attorney Docket Number:	GRTD60-35314
Receipt Date:	11-AUG-2021
Filing Date:	09-JUL-2021
Time Stamp:	12:00:40
Application Type:	Utility under 35 USC 111(a)

Payment information:

Submitted with Payment	no
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File Listing:

Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)
1	Applicant Response to Pre-Exam Formalities Notice	GRT35314ResponseNTCCORRP PRS.pdf	140749 c5bf953560418734698dda9fb92096cd615 ce9b1	no	3

Warnings:

Dell Ex. 1002

Information:					
2	Drawings-only black and white line drawings	GRT35314DWGS.pdf	3531672	no	10
			969dd9563ede422ad99ba4e86bd6299ca60c5702		
Warnings:					
Information:					
Total Files Size (in bytes):				3672421	
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25883
MUNCK WILSON MANDALA L.L.P.
P.O. Drawer 800889
DALLAS, TX 75380

CONFIRMATION NO. 2197
UPDATED FILING RECEIPT



Date Mailed: 08/13/2021

Receipt is acknowledged of this non-provisional utility patent application. The application will be taken up for examination in due course. Applicant will be notified as to the results of the examination. Any correspondence concerning the application must include the following identification information: the U.S. APPLICATION NUMBER, FILING DATE, NAME OF FIRST INVENTOR, and TITLE OF INVENTION. Fees transmitted by check or draft are subject to collection.

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Inventor(s)

G.R. MOHAN RAO, ALLEN, TX;

Applicant(s)

GREENTHREAD, LLC, Dallas, TX;

Power of Attorney: The patent practitioners associated with Customer Number 25883

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which is a CON of 16/717,950 12/17/2019 PAT 10734481
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which is a DIV of 10/934,915 09/03/2004 ABN

Foreign Applications for which priority is claimed (You may be eligible to benefit from the **Patent Prosecution Highway** program at the USPTO. Please see <http://www.uspto.gov> for more information.) - None.

Foreign application information must be provided in an Application Data Sheet in order to constitute a claim to foreign priority. See 37 CFR 1.55 and 1.76.

Permission to Access Application via Priority Document Exchange: Yes

Permission to Access Search Results: Yes

Applicant may provide or rescind an authorization for access using Form PTO/SB/39 or Form PTO/SB/69 as appropriate.

If Required, Foreign Filing License Granted: 07/22/2021

The country code and number of your priority application, to be used for filing abroad under the Paris Convention, is **US 17/371,839**

Projected Publication Date: 11/18/2021

Non-Publication Request: No

Early Publication Request: No

Title

SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS

Preliminary Class

438

Statement under 37 CFR 1.55 or 1.78 for AIA (First Inventor to File) Transition Applications: No

PROTECTING YOUR INVENTION OUTSIDE THE UNITED STATES

Since the rights granted by a U.S. patent extend only throughout the territory of the United States and have no effect in a foreign country, an inventor who wishes patent protection in another country must apply for a patent in a specific country or in regional patent offices. Applicants may wish to consider the filing of an international application under the Patent Cooperation Treaty (PCT). An international (PCT) application generally has the same effect as a regular national patent application in each PCT-member country. The PCT process **simplifies** the filing of patent applications on the same invention in member countries, but **does not result** in a grant of "an international patent" and does not eliminate the need of applicants to file additional documents and fees in countries where patent protection is desired.

Almost every country has its own patent law, and a person desiring a patent in a particular country must make an application for patent in that country in accordance with its particular laws. Since the laws of many countries differ in various respects from the patent law of the United States, applicants are advised to seek guidance from specific foreign countries to ensure that patent rights are not lost prematurely.

Applicants also are advised that in the case of inventions made in the United States, the Director of the USPTO must issue a license before applicants can apply for a patent in a foreign country. The filing of a U.S. patent application serves as a request for a foreign filing license. The application's filing receipt contains further information and guidance as to the status of applicant's license for foreign filing.

Applicants may wish to consult the USPTO booklet, "General Information Concerning Patents" (specifically, the section entitled "Treaties and Foreign Patents") for more information on timeframes and deadlines for filing foreign patent applications. The guide is available either by contacting the USPTO Contact Center at 800-786-9199, or it can be viewed on the USPTO website at <http://www.uspto.gov/web/offices/pac/doc/general/index.html>.

For information on preventing theft of your intellectual property (patents, trademarks and copyrights), you may wish to consult the U.S. Government website, <http://www.stopfakes.gov>. Part of a Department of Commerce initiative, this website includes self-help "toolkits" giving innovators guidance on how to protect intellectual property in specific

page 2 of 4

countries such as China, Korea and Mexico. For questions regarding patent enforcement issues, applicants may call the U.S. Government hotline at 1-866-999-HALT (1-866-999-4258).

LICENSE FOR FOREIGN FILING UNDER
Title 35, United States Code, Section 184
Title 37, Code of Federal Regulations, 5.11 & 5.15

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The applicant has been granted a license under 35 U.S.C. 184, if the phrase "IF REQUIRED, FOREIGN FILING LICENSE GRANTED" followed by a date appears on this form. Such licenses are issued in all applications where the conditions for issuance of a license have been met, regardless of whether or not a license may be required as set forth in 37 CFR 5.15. The scope and limitations of this license are set forth in 37 CFR 5.15(a) unless an earlier license has been issued under 37 CFR 5.15(b). The license is subject to revocation upon written notification. The date indicated is the effective date of the license, unless an earlier license of similar scope has been granted under 37 CFR 5.13 or 5.14.

This license is to be retained by the licensee and may be used at any time on or after the effective date thereof unless it is revoked. This license is automatically transferred to any related applications(s) filed under 37 CFR 1.53(d). This license is not retroactive.

The grant of a license does not in any way lessen the responsibility of a licensee for the security of the subject matter as imposed by any Government contract or the provisions of existing laws relating to espionage and the national security or the export of technical data. Licensees should apprise themselves of current regulations especially with respect to certain countries, of other agencies, particularly the Office of Defense Trade Controls, Department of State (with respect to Arms, Munitions and Implements of War (22 CFR 121-128)); the Bureau of Industry and Security, Department of Commerce (15 CFR parts 730-774); the Office of Foreign Assets Control, Department of Treasury (31 CFR Parts 500+) and the Department of Energy.

NOT GRANTED

No license under 35 U.S.C. 184 has been granted at this time, if the phrase "IF REQUIRED, FOREIGN FILING LICENSE GRANTED" DOES NOT appear on this form. Applicant may still petition for a license under 37 CFR 5.12, if a license is desired before the expiration of 6 months from the filing date of the application. If 6 months has lapsed from the filing date of this application and the licensee has not received any indication of a secrecy order under 35 U.S.C. 181, the licensee may foreign file the application pursuant to 37 CFR 5.15(b).

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technology, manufacture products, deliver services, and grow your business, visit <http://www.SelectUSA.gov> or call +1-202-482-6800.

PATENT APPLICATION FEE DETERMINATION RECORD Substitute for Form PTO-875						Application or Docket Number 17/371,839			
APPLICATION AS FILED - PART I									
(Column 1)		(Column 2)		SMALL ENTITY		OTHER THAN SMALL ENTITY			
FOR	NUMBER FILED	NUMBER EXTRA	RATE(\$)	FEE(\$)		RATE(\$)	FEE(\$)		
BASIC FEE (37 CFR 1.16(a), (b), or (c))	N/A	N/A	N/A			N/A	320		
SEARCH FEE (37 CFR 1.16(k), (l), or (m))	N/A	N/A	N/A			N/A	700		
EXAMINATION FEE (37 CFR 1.16(o), (p), or (q))	N/A	N/A	N/A			N/A	800		
TOTAL CLAIMS (37 CFR 1.16(j))	30	minus 20 = *	10			x 100 =	1000		
INDEPENDENT CLAIMS (37 CFR 1.16(h))	2	minus 3 = *				x 480 =	0.00		
APPLICATION SIZE FEE (37 CFR 1.16(s)) If the specification and drawings exceed 100 sheets of paper, the application size fee due is \$310 (\$155 for small entity) for each additional 50 sheets or fraction thereof. See 35 U.S.C. 41(a)(1)(G) and 37 CFR 1.16(s).							0.00		
							0.00		
MULTIPLE DEPENDENT CLAIM PRESENT (37 CFR 1.16(j))							0.00		
* If the difference in column 1 is less than zero, enter "0" in column 2.				TOTAL		TOTAL	2820		
APPLICATION AS AMENDED - PART II									
(Column 1)		(Column 2)		(Column 3)		SMALL ENTITY		OTHER THAN SMALL ENTITY	
AMENDMENT A		CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA	RATE(\$)	ADDITIONAL FEE(\$)	RATE(\$)	ADDITIONAL FEE(\$)
	Total (37 CFR 1.16(i))	*	Minus	**	=	x	=	x	=
	Independent (37 CFR 1.16(h))	*	Minus	***	=	x	=	x	=
	Application Size Fee (37 CFR 1.16(s))								
	FIRST PRESENTATION OF MULTIPLE DEPENDENT CLAIM (37 CFR 1.16(j))								
						TOTAL ADD'L FEE		TOTAL ADD'L FEE	
AMENDMENT B		CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA	RATE(\$)	ADDITIONAL FEE(\$)	RATE(\$)	ADDITIONAL FEE(\$)
	Total (37 CFR 1.16(i))	*	Minus	**	=	x	=	x	=
	Independent (37 CFR 1.16(h))	*	Minus	***	=	x	=	x	=
	Application Size Fee (37 CFR 1.16(s))								
	FIRST PRESENTATION OF MULTIPLE DEPENDENT CLAIM (37 CFR 1.16(j))								
						TOTAL ADD'L FEE		TOTAL ADD'L FEE	
* If the entry in column 1 is less than the entry in column 2, write "0" in column 3. ** If the "Highest Number Previously Paid For" IN THIS SPACE is less than 20, enter "20". *** If the "Highest Number Previously Paid For" IN THIS SPACE is less than 3, enter "3". The "Highest Number Previously Paid For" (Total or Independent) is the highest found in the appropriate box in column 1.									

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: G.R. Mohan Rao
Serial No.: 17/371,839
Confirmation No.: 2197
Filed: July 9, 2021
Group: 2812
Examiner: to be assigned
For: SEMICONDUCTOR DEVICES WITH GRADED DOPANT
REGIONS

Mail Stop DD
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

INFORMATION DISCLOSURE STATEMENT

In accordance with the requirements of 37 C.F.R. §§ 1.56, 1.97, and 1.98, attached please find a Form PTO SB/08 listing information for consideration by the Office in connection with its examination of the above-captioned patent application.

It is brought to Examiner's attention that the references listed on the attached Form PTO SB/08 were previously submitted to the Office in connection with a prior application, namely Application Serial No. 16/947,294, which is relied upon in the current application for an earlier filing date under 35 U.S.C. §120. Pursuant to 37 C.F.R. 1.98(d), copies of such previously submitted items are not provided herein.

Respectfully submitted,
MUNCK WILSON MANDALA, LLP
Attorneys for Applicant(s)

/Gregory M. Howison, Reg. #30646/

Gregory M. Howison
Registration No. 30,646

GMH/als
P.O. Drawer 800889
Dallas, Texas 75380
Tel: 972-628-3600
Fax: 972-628-3616
August 11, 2021

Information Disclosure Statement
SN: 17/371,839
Atty. Dkt. No. GRTD60-35314

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)	Application Number		17371839
	Filing Date		2021-07-09
	First Named Inventor	G.R. Mohan Rao	
	Art Unit	2812	
	Examiner Name		
	Attorney Docket Number	GRTD60-35314	

U.S.PATENTS						Remove
Examiner Initial*	Cite No	Patent Number	Kind Code ¹	Issue Date	Name of Patentee or Applicant of cited Document	Pages,Columns,Lines where Relevant Passages or Relevant Figures Appear
	1	4160985	A	1979-07-10	Kamins et al.	
	2	4684971	A	1987-08-04	Payne	
	3	4688063	A	1987-08-18	Lu et al.	
	4	4907058	A	1990-03-06	Sakai	
	5	4994887	A	1991-02-19	Hutter et al.	
	6	5835402	A	1998-11-10	Rao et al.	
	7	6025237	A	2000-02-15	Choi	
	8	6384431	B1	2002-05-07	Takahashi et al.	

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(Not for submission under 37 CFR 1.99)

Application Number	17371839
Filing Date	2021-07-09
First Named Inventor	G.R. Mohan Rao
Art Unit	2812
Examiner Name	
Attorney Docket Number	GRTD60-35314

9	6465862	B1	2002-10-15	Harris
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If you wish to add additional U.S. Patent citation information please click the Add button.

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U.S.PATENT APPLICATION PUBLICATIONS

Remove

Examiner Initial*	Cite No	Publication Number	Kind Code ¹	Publication Date	Name of Patentee or Applicant of cited Document	Pages, Columns, Lines where Relevant Passages or Relevant Figures Appear
	1	20010028097	A1	2001-10-11	Matsuoka et al.	
	2	20020195656	A1	2002-12-26	Hattori	
	3	20030183856	A1	2003-10-02	Wieczorek et al.	
	4	20070045682	A1	2007-03-01	Hong et al.	
	5	20080142899	A1	2008-06-19	Morris et al.	
	6	20140034997	A1	2014-02-06	Rahimo et al.	
	7	20170243876	A1	2017-08-24	Rao	

If you wish to add additional U.S. Published Application citation information please click the Add button.

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FOREIGN PATENT DOCUMENTS

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(Not for submission under 37 CFR 1.99)

Application Number	17371839
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Examiner Name	
Attorney Docket Number	GRTD60-35314

Examiner Initial*	Cite No	Foreign Document Number ³	Country Code ²	Kind Code ⁴	Publication Date	Name of Patentee or Applicant of cited Document	Pages, Columns, Lines where Relevant Passages or Relevant Figures Appear	T ⁵
	1	2003051551	JP	A	2003-02-21	Miyamoto et al.		×
	2	2003218356	JP	A	2003-07-31	Matsumoto et al.		☒
	3	6482563	JP	A	1989-03-28	Kondo		☒
	4	2004049453	WO	A1	2004-06-10	Zheng et al.		☒

If you wish to add additional Foreign Patent Document citation information please click the Add button

NON-PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, pages(s), volume-issue number(s), publisher, city and/or country where published.	T ⁵
	1	IPR2020-00288-Exhibit 1029-Claim Construction District Court 4 20-2020	
	2	IPR2020-00288-Exhibit 2007-Minutes for Markman Hearing Held Via Video Conference Before U.S. District Judge Rodney Gilstrap, Greenthread, LLC v. Samsung Electronics Co., Ltd., et al., Case No. 2:19-CV-147-JRG, Dkt. 61	
	3	IPR2020-00288-Petitioner Reply	
	4	IPR2020-00289-00289 Petitioner Reply	

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First Named Inventor	G.R. Mohan Rao
Art Unit	2812
Examiner Name	
Attorney Docket Number	GRTD60-35314

5	IPR2020-00292 - Petition for IPR
6	IPR2020-00292-Exhibit 2002-Excerpt from Exhibit 4 to Appendix B of Samsung Electronics Co., Ltd.'s Invalidity Contentions (Invalidity Contention based on U.S. Patent No. 6,384,431 to Takahashi
7	IPR2020-00288 - Ex. 1020 - Michael Nastasi and James W. Mayer, Ion Implantation and Synthesis of Materials (2006). 4 pages
8	IPR2020-00288-Exhibit 2001 - IPR2020-00288 - Excerpt from Exhibit 1 to Appendix A of Samsung Electronics Co., Ltd.'s Invalidity Contentions regarding Morris
9	IPR2020-00288-Exhibit 2002-xcerpt from Exhibit 2 to Appendix A of Samsung Electronics Co., Ltd.'s Invalidity Contentions regarding Miyamoto
10	IPR2020-00288-Exhibit 2009-Complaint for Patent Infringement, Greenthread, LLC v. Samsung Electronics Co., Ltd., et al., Case No. 2:19-CV-147-JRG, Dkt. 1
11	IPR2020-00288-Exhibit 2011- Exhibit A to Revised Joint Claim Construction Chart Pursuant to Patent Rule 4-5, Greenthread, LLC v. Samsung Electronics Co., Ltd., et al., Case No. 2:19-CV-147-JRG, Dkt. 60-1
12	IPR2020-00288-Exhibit 2012-Samsungs Responsive Claim Construction Brief - District Court
13	IPR2020-00288-Exhibit 2013- Glew Dec
14	IPR2020-00288-Exhibit 2014- Excerpt from Exhibit 10 to Appendix A of Samsung Electronics Co., Ltd.'s Invalidity Contentions
15	IPR2020-00288-Patent Owner Preliminary Response

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(Not for submission under 37 CFR 1.99)

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Filing Date		2021-07-09
First Named Inventor	G.R. Mohan Rao	
Art Unit		2812
Examiner Name		
Attorney Docket Number		GRTD60-35314

16	PR2020-00288-Patent Owner Sur Reply
17	PR2020-00288-Petition
18	PR2020-00289-Exhibit 1 to Appendix C of Samsung Electronics Co., Ltd.'s Invalidity Contentions regarding Payne
19	PR2020-00289-Exhibit 1003-Smith Dec
20	PR2020-00289-Exhibit 1010- S. M. Sze et al., Semiconductor Devices: Physics and Technology, John Wiley & Sons, 2nd Ed., 2002 ("Sze '02")
21	PR2020-00289-Exhibit 1012-Ben G. Streetman, Solid State Electronic Devices, 2nd Ed., Prentice-Hall, 1980 ("Streetman")
22	PR2020-00289-Exhibit 2001-Exhibit 1 to Appendix C of Samsung Electronics Co., Ltd.'s Invalidity Contentions regarding Payne
23	PR2020-00289-Exhibit 2002- Exhibit 3 to Appendix C of Samsung Electronics Co., Ltd.'s Invalidity Contentions regarding Wieczorek
24	PR2020-00289-Exhibit 2011-Behzad Razavi, Design of Analog CMOS Integrated Circuits, 2001 ("Razavi")
25	PR2020-00289-Exhibit 2012-Excerpts from Wolf, S., Silicon Processing for the VLSI Era, Vol.4 - Deep-Submicron Process Technology (2002) ("Wolf Vol. 4")
26	PR2020-00289-Exhibit 2013-Glew Dec

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First Named Inventor	G.R. Mohan Rao
Art Unit	2812
Examiner Name	
Attorney Docket Number	GRTD60-35314

27	PR2020-00289-Patent Owner Pre Resp
28	PR2020-00289-Patent Owner Sur reply
29	PR2020-00289-Petition
30	PR2020-00290-Exhibit 1003-Declaration of Dr. Bruce Smith
31	PR2020-00290-Exhibit 1013-Tango, Mega bit Memory Technology
32	PR2020-00290-Patent Owner Preliminary Resp
33	PR2020-00290-Patent Owner Sur Reply
34	PR2020-00290-Petition
35	PR2020-00290-Petitioners Reply to Patent Owner Preliminary Response
36	PR2020-00291-Exhibit 1003-Declaration of Dr. Bruce Smith
37	PR2020-00291-Exhibit 1011- The Insulated Gate Bipolar Transistor: IGBT Theory and Design, Vinod Kumar Khanna, IEEE Press and Wiley-Interscience, 2003

**INFORMATION DISCLOSURE
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Filing Date	2021-07-09
First Named Inventor	G.R. Mohan Rao
Art Unit	2812
Examiner Name	
Attorney Docket Number	GRTD60-35314

38	PR2020-00291-Exhibit 1020-S. M. Sze, Physics of Semiconductor Devices, Wiley-Interscience, 2nd Ed., 1981 ("Sze '81")
39	PR2020-00291-Exhibit 1021-S. M. Sze, Semiconductor Devices: Physics and Technology, John Wiley & Sons, 2nd Ed., 2002 ("Sze '02")
40	PR2020-00291-Exhibit 2001-Exhibit 2 to Appendix B of Samsung Electronics Co., LTD's Invalidity Contentions (Invalidity Contention based on U.S. Patent Application Publication No. 2002/0195656 ("Hattori"))
41	PR2020-00291-Exhibit 2013- Declaration of Dr. Alexander D. Glew
42	PR2020-00291-Patent Owner Preliminary Resp
43	PR2020-00291-Patent Owner Sur Reply
44	PR2020-00291-Petition
45	PR2020-00291-Petitioners Reply
46	PR2020-00292-Exhibit 1003-Declaration of Dr. Bruce Smith
47	PR2020-00292-Exhibit 2001-Excerpt from Exhibit 1 to Appendix B of Samsung Electronics Co., Ltd.'s Invalidity Contentions (Invalidity Contention based on "Insulated Gate Bipolar Transistor IGBT Theory and Design" by Vinod Kumar Khanna
48	PR2020-00292-Exhibit 2012-Excerpt from Exhibit A to Joint Claim Construction Chart Pursuant to Patent Rule 4-5, Greenthread, LLC v. Samsung Electronics Co., Ltd., et al., Case No. 2:19-CV-147-JRG, Dkt. 53-1 (Mar. 18, 2020)

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(Not for submission under 37 CFR 1.99)

Application Number	17371839
Filing Date	2021-07-09
First Named Inventor	G.R. Mohan Rao
Art Unit	2812
Examiner Name	
Attorney Docket Number	GRTD60-35314

49	PR2020-00292-Patent Owner Preliminary Response
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If you wish to add additional non-patent literature document citation information please click the Add button

EXAMINER SIGNATURE

Examiner Signature		Date Considered	
--------------------	--	-----------------	--

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through a citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ See Kind Codes of USPTO Patent Documents at www.USPTO.GOV or MPEP 901.04. ² Enter office that issued the document, by the two-letter code (WIPO Standard ST.3). ³ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁴ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁵ Applicant is to place a check mark here if English language translation is attached.

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(Not for submission under 37 CFR 1.99)

Application Number	17371839
Filing Date	2021-07-09
First Named Inventor	G.R. Mohan Rao
Art Unit	2812
Examiner Name	
Attorney Docket Number	GRTD60-35314

CERTIFICATION STATEMENT

Please see 37 CFR 1.97 and 1.98 to make the appropriate selection(s):

That each item of information contained in the information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement. See 37 CFR 1.97(e)(1).

OR

☐ That no item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing the certification after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in 37 CFR 1.56(c) more than three months prior to the filing of the information disclosure statement. See 37 CFR 1.97(e)(2).

See attached certification statement.

The fee set forth in 37 CFR 1.17 (p) has been submitted herewith.

☒ A certification statement is not submitted herewith.

SIGNATURE

A signature of the applicant or representative is required in accordance with CFR 1.33, 10.18. Please see CFR 1.4(d) for the form of the signature.

Signature	/Gregory M. Howison, Reg. #30646/	Date (YYYY-MM-DD)	2021-08-11
Name/Print	Gregory M. Howison	Registration Number	30646

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 1 hour to complete, including gathering, preparing and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. **DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.**

Privacy Act Statement

The Privacy Act of 1974 (P.L. 93-579) requires that you be given certain information in connection with your submission of the attached form related to a patent application or patent. Accordingly, pursuant to the requirements of the Act, please be advised that: (1) the general authority for the collection of this information is 35 U.S.C. 2(b)(2); (2) furnishing of the information solicited is voluntary; and (3) the principal purpose for which the information is used by the U.S. Patent and Trademark Office is to process and/or examine your submission related to a patent application or patent. If you do not furnish the requested information, the U.S. Patent and Trademark Office may not be able to process and/or examine your submission, which may result in termination of proceedings or abandonment of the application or expiration of the patent.

The information provided by you in this form will be subject to the following routine uses:

1. The information on this form will be treated confidentially to the extent allowed under the Freedom of Information Act (5 U.S.C. 552) and the Privacy Act (5 U.S.C. 552a). Records from this system of records may be disclosed to the Department of Justice to determine whether the Freedom of Information Act requires disclosure of these records.
2. A record from this system of records may be disclosed, as a routine use, in the course of presenting evidence to a court, magistrate, or administrative tribunal, including disclosures to opposing counsel in the course of settlement negotiations.
3. A record in this system of records may be disclosed, as a routine use, to a Member of Congress submitting a request involving an individual, to whom the record pertains, when the individual has requested assistance from the Member with respect to the subject matter of the record.
4. A record in this system of records may be disclosed, as a routine use, to a contractor of the Agency having need for the information in order to perform a contract. Recipients of information shall be required to comply with the requirements of the Privacy Act of 1974, as amended, pursuant to 5 U.S.C. 552a(m).
5. A record related to an International Application filed under the Patent Cooperation Treaty in this system of records may be disclosed, as a routine use, to the International Bureau of the World Intellectual Property Organization, pursuant to the Patent Cooperation Treaty.
6. A record in this system of records may be disclosed, as a routine use, to another federal agency for purposes of National Security review (35 U.S.C. 181) and for review pursuant to the Atomic Energy Act (42 U.S.C. 218(c)).
7. A record from this system of records may be disclosed, as a routine use, to the Administrator, General Services, or his/her designee, during an inspection of records conducted by GSA as part of that agency's responsibility to recommend improvements in records management practices and programs, under authority of 44 U.S.C. 2904 and 2906. Such disclosure shall be made in accordance with the GSA regulations governing inspection of records for this purpose, and any other relevant (i.e., GSA or Commerce) directive. Such disclosure shall not be used to make determinations about individuals.
8. A record from this system of records may be disclosed, as a routine use, to the public after either publication of the application pursuant to 35 U.S.C. 122(b) or issuance of a patent pursuant to 35 U.S.C. 151. Further, a record may be disclosed, subject to the limitations of 37 CFR 1.14, as a routine use, to the public if the record was filed in an application which became abandoned or in which the proceedings were terminated and which application is referenced by either a published application, an application open to public inspections or an issued patent.
9. A record from this system of records may be disclosed, as a routine use, to a Federal, State, or local law enforcement agency, if the USPTO becomes aware of a violation or potential violation of law or regulation.

Electronic Acknowledgement Receipt

EFS ID:	43485685
Application Number:	17371839
International Application Number:	
Confirmation Number:	2197
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS
First Named Inventor/Applicant Name:	G.R. MOHAN RAO
Customer Number:	25883
Filer:	Gregory Michael Howison
Filer Authorized By:	
Attorney Docket Number:	GRTD60-35314
Receipt Date:	13-AUG-2021
Filing Date:	09-JUL-2021
Time Stamp:	13:18:02
Application Type:	Utility under 35 USC 111(a)

Payment information:

Submitted with Payment	no
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File Listing:

Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)
1	Information Disclosure Statement (IDS) Form (SB08)	GRT35314IDSTransmittal.pdf	72988	no	1
			e400130c27c0fc12e2dff0b81893cb8d61952629		

Warnings:

Dell Ex. 1002

Page 81

Information:					
This is not an USPTO supplied IDS fillable form					
2	Information Disclosure Statement (IDS) Form (SB08)	GRT35314IDS.pdf	1055703	no	10
			28cb5924ed51719ac3d30056384a0a0d7946e1da		
Warnings:					
Information:					
			Total Files Size (in bytes):	1128691	
This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503. <u>New Applications Under 35 U.S.C. 111</u> If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application. <u>National Stage of an International Application under 35 U.S.C. 371</u> If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course. <u>New International Application Filed with the USPTO as a Receiving Office</u> If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.					



UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE
United States Patent and Trademark Office
Address: COMMISSIONER FOR PATENTS
P.O. Box 1450
Alexandria, Virginia 22313-1450
www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
17/371,839	07/09/2021	G.R. MOHAN RAO	GRTD60-35314	2197
25883	7590	10/05/2021		
MUNCK WILSON MANDALA L.L.P			EXAMINER	
P.O. Drawer 800889			CENTRAL, DOCKET	
DALLAS, TX 75380				
			ART UNIT	PAPER NUMBER
			OPAP	
			NOTIFICATION DATE	DELIVERY MODE
			10/05/2021	ELECTRONIC

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Notice of the Office communication was sent electronically on above-indicated "Notification Date" to the following e-mail address(es):

IPdocketing@munckwilson.com
admin@dalpat.com
eofficeaction@appcoll.com

<i>Decision Granting Request for Prioritized Examination (Track I)</i>	Application No. 17/371,839	Applicant(s) RAO, G.R. MOHAN	
	Examiner APRIL M WISE	Art Unit OPET	AIA (FITF) Status No
1. THE REQUEST FILED <u>09 July 2021</u> IS GRANTED . The above-identified application has met the requirements for prioritized examination A. ☒ for an original nonprovisional application (Track I). B. ☐ for an application undergoing continued examination (RCE). 2. The above-identified application will undergo prioritized examination. The application will be accorded special status throughout its entire course of prosecution until one of the following occurs: A. filing a <u>petition for extension of time</u> to extend the time period for filing a reply; B. filing an <u>amendment to amend the application to contain more than four independent claims, more than thirty total claims</u>, or a multiple dependent claim; C. filing a <u>request for continued examination</u> ; D. filing a notice of appeal; E. filing a request for suspension of action; F. mailing of a notice of allowance; G. mailing of a final Office action; H. completion of examination as defined in 37 CFR 41.102; or I. abandonment of the application. Telephone inquiries with regard to this decision should be directed to undersigned at (571)272-1642. In his/her absence, calls may be directed to Petition Help Desk at (571) 272-3282.			
/APRIL M WISE/ Paralegal Specialist, Office of Petitions			

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: G.R. Mohan RAO
Serial No.: 17/371,839
Confirmation No.: 2197
Filed: July 9, 2021
Group: 2892
Examiner: Ajay ARORA
For: SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS

Mail Stop Petitions
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

PETITION TO EXPUNGE ASSIGNMENT RECORDING

Petitioner respectfully petitions to suspend the rules under 37 C.F.R. § 1.182 and requests that Assignment: 2, i.e., from Greenthread, LLC to Vervain, LLC be deleted to reflect the correct ownership of the patent. The reasons why justice requires a waiver of the requirements are as follows:

- The normal corrective procedures as outlined in MPEP § 323.01(a) through § 323.01(c) will not provide petitioners with adequate relief.
- An assignment totally unrelated to the current application was incorrectly recorded in the application. (A copy of the recorded Assignment document is attached)
- The assignment recordation error is not of a typographical nature; thus, MPEP § 323.01(a) does not apply.
- The recorded assignment document does not contain a typographical error and, additionally, matches the cover sheet. As such, MPEP § 323.01(b) does not apply.
- The assignment was not improperly filed and recorded by another person against the current Application. Therefore, MPEP § 323.01(c) does not apply.

PETITION TO EXPUNGE ASSIGNMENT RECORDING

S/N 17/371,839

Atty. Dkt. No. GRTD60-35314

1

Thus,

- There never existed an assignment from Greenthread, LLC to Vervain, LLC with respect to U.S. Application No. 17/371,839 or any applications or patents related to it. (A copy of the USPTO Parent Continuity Data is attached.)
- The recorded assignment is void and should be expunged from the record.
- No right, title or interest was transferred to any existing entity as the result of this recorded document.
- All right, title and interest remain as originally recorded, from inventor G.R. Mohan Rao to Greenthread, LLC.
- There was no intent to assign the patent from Greenthread, LLC to Vervain, LLC, and such recordation was made in error.

For the reasons set forth above, Petitioner respectfully requests that this Petition be granted. Petitioner submits that the integrity of the assignment records will not be affected by the granting of the petition.

Accordingly, Petitioner requests expunction of the recorded assignment from Greenthread, LLC to Vervain, LLC such that all right, title and interest remain in Greenthread, LLC.

Enclosed is the fee of \$420.00 as set forth under C.F.R. 1.17(f). Please charge any deficiency or credit any overpayment to deposit account number 50-0208/GRTD60-35314 of MUNCK, WILSON, MANDALA, LLP.

Respectfully submitted,
MUNCK, WILSON, MANDALA, LLP
Attorneys for Petitioners

/Gregory M. Howison, Reg. #30646/

Gregory M. Howison
Registration No. 30,646

GMH/als
P.O. Drawer 800889
Dallas, Texas 75380
Tel: 972-628-3600
Fax: 972-628-3616
October 19, 2021

PETITION TO EXPUNGE ASSIGNMENT RECORDING
S/N 17/371,839
Atty. Dkt. No. GRTD60-35314

ASSIGNOR Greenthread, LLC Philip W. John, Jr. Manager 6307 Bandera Ave, Apt B Dallas, Texas 75225-3617 Email: john@greenthreadllc.com	ASSIGNEE Vervain, LLC Philip W. John, Jr., Member 7424 Mason Dells Drive Dallas, Texas 75230-3244 Email: john@vervainllc.com
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ASSIGNMENT AGREEMENT

This Assignment Agreement ("Assignment") is entered into by and between Vervain, LLC, a Texas limited liability company, hereinafter referred to as "Assignee," and Greenthread, LLC, a Texas limited liability company, hereinafter referred to as "Assignor," and shall become effective upon being duly signed by the authorized representative of Assignor ("Effective Date").

RECITALS:

Assignor and Assignee are entering into a Patent Assignment Agreement (the "Agreement").

Pursuant to the Agreement, Assignor hereby desires to assign to Assignee all of its rights, title and interest in and to the following United States patents and pending application:

1. U.S. Provisional Application Number 61/509,256, entitled, "Lifetime Mixed Level Nand Flash System," filed on July 19, 2011;
2. U.S. Patent Number 8,891,298, entitled, "Lifetime Mixed Level Non-Volatile Memory System," filed on April 25, 2012, and issued on November 18, 2014;
3. U.S. Patent Number 9,196,385, entitled, "Lifetime Mixed Level Non-Volatile Memory System," filed on October 28, 2014, and issued on November 24, 2015;
4. U.S. Patent Number 9,997,240, entitled, "Lifetime Mixed Level Non-Volatile Memory System," filed on November 24, 2015, and issued on June 12, 2018, and
5. U.S. Patent Application Number 16/006,299, entitled, "Lifetime Mixed Level Non-Volatile Memory System," filed on June 12, 2018, and is pending (collectively referred to hereinafter referred to as the "Patent").

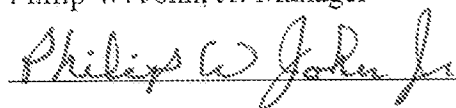
For good and valuable consideration, Assignor and Assignee hereby agree as follows:

ASSIGNMENT:

1. Assignor hereby assigns to Assignee its entire worldwide right, title and interest in and to Assignor's Patent, including the entire worldwide right, title and interest in and to any reexamination or reissue of the Patent. This includes, without limitation, Assignor's right to prosecute, and receive, all damages, royalties, awards and compensation for past, present and/or future infringement.
2. Assignor agrees to do the following without further consideration, in order to carry out the intent of this Assignment:
 - i. Execute all oaths, assignments, applications, and other papers necessary or desirable to fully secure to Assignee the rights, titles and interests herein conveyed; and
 - ii. Generally do all lawful acts for vesting in Assignee the rights, titles, and interests herein conveyed.
3. Assignor has not made and will not hereafter make any assignment, grant, mortgage, license, or other agreement affecting the rights, titles, and interests herein conveyed to Assignee.
4. Assignor hereby represents and warrants that Assignor has the authority to assign the applicable Patent pursuant to this Assignment.

The undersigned having read this Assignment and fully understanding the provisions of this Assignment, hereby executes this Assignment as of the Effective Date.

Greenthread, LLC (Assignor)
Philip W. John, Jr. Manager



Signature:

Printed Name: Philip W. John, Jr.

Date: August 9, 2019

Parent Continuity Data

Description	Parent Number	Parent Filing or 371(c) Date	AIA (First Inventor to File)	Parent Status	Patent Number
This application is a Continuation of	16/947,294	07-27-2020	No	Patented	11,121,222
is a continuation of	16/717,950	12-17-2019	No	Patented	10,734,481
is a continuation of	15/590,282	05-09-2017	No	Patented	10,510,842
is a continuation of	14/931,636	11-03-2015	No	Patented	9,647,070
is a continuation of	14/515,584	10-16-2014	No	Patented	9,190,502
is a continuation of	13/854,319	04-01-2013	No	Abandoned	-
is a continuation of	11/622,496	01-12-2007	No	Patented	8,421,195
is a Division of	10/934,915	09-03-2004	No	Abandoned	-

Child Continuity Data

No Child Continuity Data Found

Close Window

Electronic Patent Application Fee Transmittal

Application Number:	17371839			
Filing Date:	09-Jul-2021			
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS			
First Named Inventor/Applicant Name:	G.R. MOHAN RAO			
Filer:	Gregory Michael Howison/Anna Nguyen			
Attorney Docket Number:	GRTD60-35314			
Filed as Large Entity				
Filing Fees for Utility under 35 USC 111(a)				
Description	Fee Code	Quantity	Amount	Sub-Total in USD(\$)
Basic Filing:				
Pages:				
Claims:				
Miscellaneous-Filing:				
Petition:				
PETITION FEE- 37 CFR 1.17(F) (GROUP I)	1462	1	420	420
Patent-Appeals-and-Interference:				
Post-Allowance-and-Post-Issuance:				

Description	Fee Code	Quantity	Amount	Sub-Total in USD(\$)
Extension-of-Time:				
Miscellaneous:				
Total in USD (\$)				420

Electronic Acknowledgement Receipt

EFS ID:	44060872
Application Number:	17371839
International Application Number:	
Confirmation Number:	2197
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS
First Named Inventor/Applicant Name:	G.R. MOHAN RAO
Customer Number:	25883
Filer:	Gregory Michael Howison
Filer Authorized By:	
Attorney Docket Number:	GRTD60-35314
Receipt Date:	19-OCT-2021
Filing Date:	09-JUL-2021
Time Stamp:	11:10:49
Application Type:	Utility under 35 USC 111(a)

Payment information:

Submitted with Payment	yes
Payment Type	DA
Payment was successfully received in RAM	\$420
RAM confirmation Number	E20210IB11500206
Deposit Account	500208
Authorized User	Gregory Howison

The Director of the USPTO is hereby authorized to charge indicated fees and credit any overpayment as follows:

37 CFR 1.21 (Miscellaneous fees and charges)

37 CFR 1.20 (Post Issuance fees)

Dell Ex. 1002

Page 92

File Listing:

Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)
1	Petition for review by the Office of Petitions	GRT35314PetitiontoExpunge.pdf	1713018	no	5
			c055f20e57ec2274e0cd97b77d2df6f98953b462		

Warnings:**Information:**

2	Fee Worksheet (SB06)	fee-info.pdf	38237	no	2
			ffd80fae29ff2a114a9e9cd93834d8403b477dbc		

Warnings:**Information:**

Total Files Size (in bytes):	1751255
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This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503.

New Applications Under 35 U.S.C. 111

If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.

National Stage of an International Application under 35 U.S.C. 371

If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.

New International Application Filed with the USPTO as a Receiving Office

If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.



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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
17/371,839	07/09/2021	G.R. MOHAN RAO	GRTD60-35314	2197
25883	7590	10/28/2021		
MUNCK WILSON MANDALA L.L.P			EXAMINER	
P.O. Drawer 800889			ARORA, AJAY	
DALLAS, TX 75380				
			ART UNIT	PAPER NUMBER
			2892	
			NOTIFICATION DATE	DELIVERY MODE
			10/28/2021	ELECTRONIC

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Notice of the Office communication was sent electronically on above-indicated "Notification Date" to the following e-mail address(es):

IPdocketing@munckwilson.com
admin@dalpat.com
eofficeaction@appcoll.com

Office Action Summary**Application No.**

17/371,839

Applicant(s)

RAO, G.R. MOHAN

Examiner

AJAY ARORA

Art Unit

2892

AIA (FITF) Status

No

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTHS FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

1) ☒ Responsive to communication(s) filed on 7/9/2021.

☐ A declaration(s)/affidavit(s) under **37 CFR 1.130(b)** was/were filed on ____.

2a) ☐ This action is **FINAL**.

2b) ☒ This action is non-final.

3) ☐ An election was made by the applicant in response to a restriction requirement set forth during the interview on ____; the restriction requirement and election have been incorporated into this action.

4) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims*

5) ☒ Claim(s) 1-30 is/are pending in the application.

5a) Of the above claim(s) ____ is/are withdrawn from consideration.

6) ☐ Claim(s) ____ is/are allowed.

7) ☒ Claim(s) 1-30 is/are rejected.

8) ☐ Claim(s) ____ is/are objected to.

9) ☐ Claim(s) ____ are subject to restriction and/or election requirement

* If any claims have been determined allowable, you may be eligible to benefit from the **Patent Prosecution Highway** program at a participating intellectual property office for the corresponding application. For more information, please see http://www.uspto.gov/patents/init_events/pph/index.jsp or send an inquiry to PPHfeedback@uspto.gov.

Application Papers

10) ☐ The specification is objected to by the Examiner.

11) ☒ The drawing(s) filed on 8/11/2021 is/are: a) ☒ accepted or b) ☐ objected to by the Examiner.

Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).

Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).

Priority under 35 U.S.C. § 119

12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).

Certified copies:

a) ☐ All b) ☐ Some** c) ☐ None of the:

1. ☐ Certified copies of the priority documents have been received.

2. ☐ Certified copies of the priority documents have been received in Application No. ____.

3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

** See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

1) ☒ Notice of References Cited (PTO-892)

3) ☐ Interview Summary (PTO-413)

Paper No(s)/Mail Date ____.

2) ☒ Information Disclosure Statement(s) (PTO/SB/08a and/or PTO/SB/08b)

4) ☐ Other: ____.

Paper No(s)/Mail Date 8/13/2021.

DETAILED ACTION

Notice of Pre-AIA or AIA Status

1. The present application is being examined under the pre-AIA first to invent provisions.

Double Patenting

2. A rejection based on double patenting of the “same invention” type finds its support in the language of 35 U.S.C. 101 which states that “whoever invents or discovers any new and useful process... may obtain a patent therefor...” (Emphasis added). Thus, the term “same invention,” in this context, means an invention drawn to identical subject matter. See *Miller v. Eagle Mfg. Co.*, 151 U.S. 186 (1894); *In re Vogel*, 422 F.2d 438, 164 USPQ 619 (CCPA 1970); *In re Ockert*, 245 F.2d 467, 114 USPQ 330 (CCPA 1957).

A statutory type (35 U.S.C. 101) double patenting rejection can be overcome by canceling or amending the claims that are directed to the same invention so they are no longer coextensive in scope. The filing of a terminal disclaimer cannot overcome a double patenting rejection based upon 35 U.S.C. 101.

3. Claims 1-30, respectively, are provisionally rejected under 35 U.S.C. 101 as claiming the same invention as that of claims 1-30, respectively, of copending Application No. 16/947,294 (reference application). This is a provisional statutory double patenting rejection since the claims directed to the same invention have not in fact been

patented (although a Notice of Allowance for application 16/947,294 dated 8/11/2021 has been issued, a patent has not yet been issued).

Art Based Rejection

4. No art based rejection has been provided, as the prior art does not teach or suggest the features of claims 1-30. The closest prior art is Hong (US 2007/0045682), hereinafter Hong, especially see Figures 4A-4D and 5A-5C and para 26-32 (as also explained in Notice of Allowance of 8/11/2021 for parent application 16/947,294).

Conclusion

5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to AJAY ARORA whose telephone number is (571)272-8347. The examiner can normally be reached 9 AM - 5 PM.

Examiner interviews are available via telephone, in-person, and video conferencing using a USPTO supplied web-based collaboration tool. To schedule an interview, applicant is encouraged to use the USPTO Automated Interview Request (AIR) at <http://www.uspto.gov/interviewpractice>.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Thao X. Le can be reached on 5712721708. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of published or unpublished applications may be obtained from Patent Center. Unpublished application information in Patent Center is available to registered users. To file and manage patent submissions in Patent Center,

visit: <https://patentcenter.uspto.gov>. Visit <https://www.uspto.gov/patents/apply/patent-center> for more information about Patent Center and <https://www.uspto.gov/patents/docx> for information about filing in DOCX format. For additional questions, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/AJAY ARORA/
Primary Examiner, Art Unit 2892

<i>Notice of References Cited</i>	Application/Control No. 17/371,839		Applicant(s)/Patent Under Reexamination RAO, G.R. MOHAN	
	Examiner AJAY ARORA		Art Unit 2892	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	CPC Classification	US Classification
*	A	US-20070045682-A1	03-2007	Hong; Sungkwon C.	H01L27/14689	257/292
*	B	US-20140034997-A1	02-2014	RAHIMO; Munaf	H01L29/861	257/139
	C					
	D					
	E					
	F					
	G					
	H					
	I					
	J					
	K					
	L					
	M					

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	CPC Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	
	V	
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

Search Notes 	Application/Control No. 17/371,839	Applicant(s)/Patent Under Reexamination RAO, G.R. MOHAN
	Examiner AJAY ARORA	Art Unit 2892

CPC - Searched*		
Symbol	Date	Examiner
H01L 29/1095	10/23/2021	AKA

CPC Combination Sets - Searched*		
Symbol	Date	Examiner

US Classification - Searched*			
Class	Subclass	Date	Examiner
257	25	10/23/2021	AKA

* See search history printout included with this form or the SEARCH NOTES box below to determine the scope of the search.

Search Notes		
Search Notes	Date	Examiner
Inventor search	10/23/2021	AKA
Assignee search	10/23/2021	AKA
References for all parent applications (10/934,915; 11/622,496; 15/590,282; 16/717950 and 16/947294) considered	10/23/2021	AKA
.clm. interference search	10/23/2021	AKA
EAST search history report	10/23/2021	AKA

Interference Search			
US Class/CPC Symbol	US Subclass/CPC Group	Date	Examiner
H01L	29/1095	10/23/2021	AKA
257	25	10/23/2021	AKA

/AJAY ARORA/ Primary Examiner, Art Unit 2892	
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<i>Search Notes</i> 	Application/Control No. 17/371,839	Applicant(s)/Patent Under Reexamination RAO, G.R. MOHAN
	Examiner AJAY ARORA	Art Unit 2892

/AJAY ARORA/ Primary Examiner, Art Unit 2892	
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<i>Index of Claims</i> 	Application/Control No. 17/371,839	Applicant(s)/Patent Under Reexamination RAO, G.R. MOHAN
	Examiner AJAY ARORA	Art Unit 2892

✓	Rejected	-	Cancelled	N	Non-Elected	A	Appeal
=	Allowed	÷	Restricted	I	Interference	O	Objected

CLAIMS										
☐ Claims renumbered in the same order as presented by applicant ☐ CPA ☐ T.D. ☐ R.1.47										
CLAIM		DATE								
Final	Original	10/23/2021								
	1	✓								
	2	✓								
	3	✓								
	4	✓								
	5	✓								
	6	✓								
	7	✓								
	8	✓								
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	25	✓								
	26	✓								
	27	✓								
	28	✓								
	29	✓								
	30	✓								

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	574	(source drain source/drain) and drift and ((gradient graded) near2 concentration near2 dop\$3) and well	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23 15:37
L3	574	L2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23 15:37
L4	1	("9647070").PN.	US-PGPUB; USPAT	OR	OFF	2021/10/23 16:21
L5	1	("6384431").PN.	US-PGPUB; USPAT	OR	OFF	2021/10/23 16:21
S1	0	17/371,839	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23 10:17
S2	31	((("GREENTHREAD") near3 ("LLC"))).AS,AANM.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2021/10/23 10:18
S3	29	((("RAO") near3 ("G.R") near3 ("MOHAN"))).INV.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2021/10/23 10:19
S4	30,065	H01L29/1095.cpc.	US-PGPUB; USPAT; USOCR; FPRS; EPO;	OR	OFF	2021/10/23 10:19

			JPO; DERWENT; IBM_TDB			
S5	669	(257/25).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23 10:19
S6	56	("20010028097" "20020195656" "20030183856" "20070045682" "20080142899" "20140034997" "20170243876" "4160985" "4684971" "4688063" "4907058" "4994887" "5835402" "6025237" "6384431" "6465862").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2021/10/23 10:20
S7	29	("5448087" "5888857" "20030030488" "6720622" "20030026126" "5973575" "5262345" "20040027753").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23 10:20
S8	12	(US-20040027753-\$ or US- 20030030488-\$ or US-20140034997-\$ or US-20060049464-\$ or US- 20030026126-\$ or US-20070181927-\$ or US-20070045682-\$).did. or (US- 5973575-\$ or US-5262345-\$ or US- 5448087-\$ or US-6720622-\$ or US- 5888857-\$).did.	US-PGPUB; USPAT	OR	ON	2021/10/23 10:21
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S10	118	("20020074585" "5496746" "6683343" "6696314" "6452086" "6472715" "6747883" "5797999" "6670544" "20040063288" "4347654" "4866000" "6744117" "6754093" "5213988" "5569612" "RE37441" "4001864" "6756616" "5130262" "5329144" "6706550" "6753202" "5480816" "6713813" "6737722" "5575862" "6211028").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23 10:23

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S15	10	S3 and drift	US-PGPUB; USPAT;	OR	OFF	2021/10/23 11:02

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S16	14	S2 and drift	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23 11:02
S17	574	(source drain source/drain) and drift and ((gradient graded) near2 concentration near2 dop\$3) and well	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23 11:03
S18	25,930	H01L27/11521.cpc.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2021/10/23 11:03
S19	14,669	H01L27/11524.cpc.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2021/10/23 11:04
S20	29,711	H01L27/14643.cpc.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2021/10/23 11:04
S21	11,836	H01L29/36.cpc.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2021/10/23 11:04
S22	13,097	H01L29/7395.cpc.	US-PGPUB; USPAT; USOCR;	OR	ON	2021/10/23 11:04

			FPRS; EPO; JPO; DERWENT; IBM_TDB			
S23	18	S4 and S18 and S21	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2021/10/23 11:08
S24	18	S4 and S18 and S20	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2021/10/23 11:10
S25	18	S4 and S19 and S20	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2021/10/23 11:10
S26	66	S4 and S19 and S21	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2021/10/23 11:10
S27	2	((source drain "source/drain" active) and drift and ((gradient graded) near2 concentration near2 dop\$3) and well and ((no near2 active) (inactive))).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23 11:11
S28	32	((source drain "source/drain" active) and drift and ((gradient graded) near2 concentration near2 dop\$3) and well and ((no near2 active) (inactive)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23 11:13

10/23/2021 4:35:05 PM

C:\Users\aarora\Documents\EAST\Workspaces\17371839.wsp

Doc code: IDS

PTO/SB/08a (02-18)

Doc description: Information Disclosure Statement (IDS) Filed

Approved for use through 11/30/2020. OMB 0651-0031

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)

Application Number	17371839
Filing Date	2021-07-09
First Named Inventor	G.R. Mohan Rao
Art Unit	2812
Examiner Name	
Attorney Docket Number	GRTD60-35314

U.S.PATENTS						Remove
Examiner Initial*	Cite No	Patent Number	Kind Code ¹	Issue Date	Name of Patentee or Applicant of cited Document	Pages,Columns,Lines where Relevant Passages or Relevant Figures Appear
/A.A/	1	4160985	A	1979-07-10	Kamins et al.	
/A.A/	2	4684971	A	1987-08-04	Payne	
/A.A/	3	4688063	A	1987-08-18	Lu et al.	
/A.A/	4	4907058	A	1990-03-06	Sakai	
/A.A/	5	4994887	A	1991-02-19	Hutter et al.	
/A.A/	6	5835402	A	1998-11-10	Rao et al.	
/A.A/	7	6025237	A	2000-02-15	Choi	
/A.A/	8	6384431	B1	2002-05-07	Takahashi et al.	

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /A.A/

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Attorney Docket Number	GRTD60-35314

/A.A/	9	6465862	B1	2002-10-15	Harris
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Examiner Initial*	Cite No	Publication Number	Kind Code ¹	Publication Date	Name of Patentee or Applicant of cited Document	Pages, Columns, Lines where Relevant Passages or Relevant Figures Appear
/A.A/	1	20010028097	A1	2001-10-11	Matsuoka et al.	
/A.A/	2	20020195656	A1	2002-12-26	Hattori	
/A.A/	3	20030183856	A1	2003-10-02	Wieczorek et al.	
/A.A/	4	20070045682	A1	2007-03-01	Hong et al.	
/A.A/	5	20080142899	A1	2008-06-19	Morris et al.	
/A.A/	6	20140034997	A1	2014-02-06	Rahimo et al.	
/A.A/	7	20170243876	A1	2017-08-24	Rao	

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Examiner Initial*	Cite No	Foreign Document Number ³	Country Code ²	Kind Code ⁴	Publication Date	Name of Patentee or Applicant of cited Document	Pages, Columns, Lines where Relevant Passages or Relevant Figures Appear	T ⁵
/A.A/	1	2003051551	JP	A	2003-02-21	Miyamoto et al.		×
/A.A/	2	2003218356	JP	A	2003-07-31	Matsumoto et al.		☒
/A.A/	3	6482563	JP	A	1989-03-28	Kondo		☒
/A.A/	4	2004049453	WO	A1	2004-06-10	Zheng et al.		☒

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NON-PATENT LITERATURE DOCUMENTS

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Examiner Initials*	Cite No	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, pages(s), volume-issue number(s), publisher, city and/or country where published.	T ⁵
	1	IPR2020-00288-Exhibit 1029-Claim Construction District Court 4 20-2020	
	2	IPR2020-00288-Exhibit 2007-Minutes for Markman Hearing Held Via Video Conference Before U.S. District Judge Rodney Gilstrap, Greenthread, LLC v. Samsung Electronics Co., Ltd., et al., Case No. 2:19-CV-147-JRG, Dkt. 61	
	3	IPR2020-00288-Petitioner Reply	
	4	IPR2020-00289-00289 Petitioner Reply	

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Examiner Name	
Attorney Docket Number	GRTD60-35314

5	IPR2020-00292 - Petition for IPR
6	IPR2020-00292-Exhibit 2002-Excerpt from Exhibit 4 to Appendix B of Samsung Electronics Co., Ltd.'s Invalidity Contentions (Invalidity Contention based on U.S. Patent No. 6,384,431 to Takahashi
7	IPR2020-00288 - Ex. 1020 - Michael Nastasi and James W. Mayer, Ion Implantation and Synthesis of Materials (2006). 4 pages
8	IPR2020-00288-Exhibit 2001 - IPR2020-00288 - Excerpt from Exhibit 1 to Appendix A of Samsung Electronics Co., Ltd.'s Invalidity Contentions regarding Morris
9	IPR2020-00288-Exhibit 2002-xcerpt from Exhibit 2 to Appendix A of Samsung Electronics Co., Ltd.'s Invalidity Contentions regarding Miyamoto
10	IPR2020-00288-Exhibit 2009-Complaint for Patent Infringement, Greenthread, LLC v. Samsung Electronics Co., Ltd., et al., Case No. 2:19-CV-147-JRG, Dkt. 1
11	IPR2020-00288-Exhibit 2011- Exhibit A to Revised Joint Claim Construction Chart Pursuant to Patent Rule 4-5, Greenthread, LLC v. Samsung Electronics Co., Ltd., et al., Case No. 2:19-CV-147-JRG, Dkt. 60-1
12	IPR2020-00288-Exhibit 2012-Samsungs Responsive Claim Construction Brief - District Court
13	IPR2020-00288-Exhibit 2013- Glew Dec
14	IPR2020-00288-Exhibit 2014- Excerpt from Exhibit 10 to Appendix A of Samsung Electronics Co., Ltd.'s Invalidity Contentions
15	IPR2020-00288-Patent Owner Preliminary Response

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Attorney Docket Number	GRTD60-35314

16	PR2020-00288-Patent Owner Sur Reply
17	PR2020-00288-Petition
18	PR2020-00289-Exhibit 1 to Appendix C of Samsung Electronics Co., Ltd.'s Invalidity Contentions regarding Payne
19	PR2020-00289-Exhibit 1003-Smith Dec
20	PR2020-00289-Exhibit 1010- S. M. Sze et al., Semiconductor Devices: Physics and Technology, John Wiley & Sons, 2nd Ed., 2002 ("Sze '02")
21	PR2020-00289-Exhibit 1012-Ben G. Streetman, Solid State Electronic Devices, 2nd Ed., Prentice-Hall, 1980 ("Streetman")
22	PR2020-00289-Exhibit 2001-Exhibit 1 to Appendix C of Samsung Electronics Co., Ltd.'s Invalidity Contentions regarding Payne
23	PR2020-00289-Exhibit 2002- Exhibit 3 to Appendix C of Samsung Electronics Co., Ltd.'s Invalidity Contentions regarding Wieczorek
24	PR2020-00289-Exhibit 2011-Behzad Razavi, Design of Analog CMOS Integrated Circuits, 2001 ("Razavi")
25	PR2020-00289-Exhibit 2012-Excerpts from Wolf, S., Silicon Processing for the VLSI Era, Vol.4 - Deep-Submicron Process Technology (2002) ("Wolf Vol. 4")
26	PR2020-00289-Exhibit 2013-Glew Dec

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Art Unit	2812
Examiner Name	
Attorney Docket Number	GRTD60-35314

27	PR2020-00289-Patent Owner Pre Resp
28	PR2020-00289-Patent Owner Sur reply
29	PR2020-00289-Petition
30	PR2020-00290-Exhibit 1003-Declaration of Dr. Bruce Smith
31	PR2020-00290-Exhibit 1013-Tango, Mega bit Memory Technology
32	PR2020-00290-Patent Owner Preliminary Resp
33	PR2020-00290-Patent Owner Sur Reply
34	PR2020-00290-Petition
35	PR2020-00290-Petitioners Reply to Patent Owner Preliminary Response
36	PR2020-00291-Exhibit 1003-Declaration of Dr. Bruce Smith
37	PR2020-00291-Exhibit 1011- The Insulated Gate Bipolar Transistor: IGBT Theory and Design, Vinod Kumar Khanna, IEEE Press and Wiley-Interscience, 2003

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Attorney Docket Number	GRTD60-35314

38	PR2020-00291-Exhibit 1020-S. M. Sze, Physics of Semiconductor Devices, Wiley-Interscience, 2nd Ed., 1981 ("Sze '81")
39	PR2020-00291-Exhibit 1021-S. M. Sze, Semiconductor Devices: Physics and Technology, John Wiley & Sons, 2nd Ed., 2002 ("Sze '02")
40	PR2020-00291-Exhibit 2001-Exhibit 2 to Appendix B of Samsung Electronics Co., LTD's Invalidity Contentions (Invalidity Contention based on U.S. Patent Application Publication No. 2002/0195656 ("Hattori"))
41	PR2020-00291-Exhibit 2013- Declaration of Dr. Alexander D. Glew
42	PR2020-00291-Patent Owner Preliminary Resp
43	PR2020-00291-Patent Owner Sur Reply
44	PR2020-00291-Petition
45	PR2020-00291-Petitioners Reply
46	PR2020-00292-Exhibit 1003-Declaration of Dr. Bruce Smith
47	PR2020-00292-Exhibit 2001-Excerpt from Exhibit 1 to Appendix B of Samsung Electronics Co., Ltd.'s Invalidity Contentions (Invalidity Contention based on "Insulated Gate Bipolar Transistor IGBT Theory and Design" by Vinod Kumar Khanna
48	PR2020-00292-Exhibit 2012-Excerpt from Exhibit A to Joint Claim Construction Chart Pursuant to Patent Rule 4-5, Greenthread, LLC v. Samsung Electronics Co., Ltd., et al., Case No. 2:19-CV-147-JRG, Dkt. 53-1 (Mar. 18, 2020)

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Filing Date	2021-07-09	
First Named Inventor	G.R. Mohan Rao	
Art Unit	2812	
Examiner Name		
Attorney Docket Number	GRTD60-35314	

49	PR2020-00292-Patent Owner Preliminary Response
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EXAMINER SIGNATURE

Examiner Signature	/AJAY ARORA/	Date Considered	10/23/2021
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through a citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ See Kind Codes of USPTO Patent Documents at www.USPTO.GOV or MPEP 901.04. ² Enter office that issued the document, by the two-letter code (WIPO Standard ST.3). ³ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁴ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁵ Applicant is to place a check mark here if English language translation is attached.

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /A.A/

Copies of non-patent literature documents listed not provided in current application but provided in parent application 16/947,294

**INFORMATION DISCLOSURE
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First Named Inventor	G.R. Mohan Rao
Art Unit	2812
Examiner Name	
Attorney Docket Number	GRTD60-35314

CERTIFICATION STATEMENT

Please see 37 CFR 1.97 and 1.98 to make the appropriate selection(s):

That each item of information contained in the information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement. See 37 CFR 1.97(e)(1).

OR

☐ That no item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing the certification after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in 37 CFR 1.56(c) more than three months prior to the filing of the information disclosure statement. See 37 CFR 1.97(e)(2).

See attached certification statement.

The fee set forth in 37 CFR 1.17 (p) has been submitted herewith.

☒ A certification statement is not submitted herewith.

SIGNATURE

A signature of the applicant or representative is required in accordance with CFR 1.33, 10.18. Please see CFR 1.4(d) for the form of the signature.

Signature	/Gregory M. Howison, Reg. #30646/	Date (YYYY-MM-DD)	2021-08-11
Name/Print	Gregory M. Howison	Registration Number	30646

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 1 hour to complete, including gathering, preparing and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. **SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.**

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4. A record in this system of records may be disclosed, as a routine use, to a contractor of the Agency having need for the information in order to perform a contract. Recipients of information shall be required to comply with the requirements of the Privacy Act of 1974, as amended, pursuant to 5 U.S.C. 552a(m).
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APPLICATION NUMBER	FILING OR 371(C) DATE	FIRST NAMED APPLICANT	ATTY. DOCKET NO./TITLE
17/371,839	07/09/2021	G.R. MOHAN RAO	GRTD60-35314

CONFIRMATION NO. 2197

25883
MUNCK WILSON MANDALA L.L.P
P.O. Drawer 800889
DALLAS, TX 75380

PUBLICATION NOTICE



OC000000129896952

Title:SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS

Publication No.US-2021-0359086-A1

Publication Date:11/18/2021

NOTICE OF PUBLICATION OF APPLICATION

The above-identified application will be electronically published as a patent application publication pursuant to 37 CFR 1.211, et seq. The patent application publication number and publication date are set forth above.

The publication may be accessed through the USPTO's publically available Searchable Databases via the Internet at www.uspto.gov. The direct link to access the publication is currently <http://www.uspto.gov/patft/>.

The publication process established by the Office does not provide for mailing a copy of the publication to applicant. A copy of the publication may be obtained from the Office upon payment of the appropriate fee set forth in 37 CFR 1.19(a)(1). Orders for copies of patent application publications are handled by the USPTO's Public Records Division. The Public Records Division can be reached by telephone at (571) 272-3150 or (800) 972-6382, by facsimile at (571) 273-3250, by mail addressed to the United States Patent and Trademark Office, Public Records Division, Alexandria, VA 22313-1450 or via the Internet.

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Office of Data Management, Application Assistance Unit (571) 272-4000, or (571) 272-4200, or 1-888-786-0101

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: G.R. MOHAN RAO
Serial No.: 17/371,839
Confirmation No.: 2197
Filed: July 9, 2021
Group: 2892
Examiner: Ajay ARORA
For: SEMICONDUCTOR DEVICES WITH GRADED DOPANT
REGIONS

Mail Stop AMENDMENT
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

AMENDMENT AND RESPONSE TO OFFICE ACTION

This communication is responsive to the Examiner's Office Action dated October 28, 2021.
Reconsideration is respectfully requested.

Amendments to the Claims are reflected in the listing of claims beginning on page 2 of this paper.
Remarks/Arguments begin on page 7 of this paper.

In the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) An electronic system ~~VLSI semiconductor device~~, the system comprising:

at least one semiconductor device, the at least one semiconductor device including:

a substrate of a first doping type at a first doping level having a surface;

a first active region disposed adjacent the surface with a second doping type opposite in conductivity to the first doping type and within which transistors can be formed;

a second active region separate from the first active region disposed adjacent to the first active region and within which transistors can be formed;

transistors formed in at least one of the first active region or second active region;

at least a portion of at least one of the first and second active regions having at least one graded dopant concentration to aid carrier movement from the first and second active regions towards an area of the substrate where there are no active regions; and

at least one well region adjacent to the first or second active region containing at least one graded dopant region, the graded dopant region to aid carrier movement from the surface towards the area of the substrate where there are no active regions, wherein at least some of the transistors form digital logic of the ~~[[VLSI]]~~ semiconductor device.

2. (Currently amended) The system ~~VLSI semiconductor device~~ of Claim 1, wherein the substrate of the at least one semiconductor device is a p-type substrate.

3. (Currently amended) The system ~~VLSI semiconductor device~~ of Claim 1, wherein the substrate of the at least one semiconductor device has epitaxial silicon on top of a nonepitaxial substrate.
4. (Currently amended) The system ~~VLSI semiconductor device~~ of Claim 1, wherein the first active region and second active region of the at least one semiconductor device contain digital logic formed by one of either p-channel and n-channel devices.
5. (Currently amended) The system ~~VLSI semiconductor device~~ of Claim 1, wherein the first active region and second active region of the at least one semiconductor device contain either p-channel or n-channel devices in n-wells or p-wells, respectively, and each well has at least one graded dopant.
6. (Currently amended) The system ~~VLSI semiconductor device~~ of Claim 1, wherein the first active region and second active region of the at least one semiconductor device are each separated by at least one isolation region.
7. (Currently amended) The system ~~VLSI semiconductor device~~ of Claim 1, wherein the graded dopant is fabricated with an ion implantation process.
8. (Currently amended) The system ~~VLSI semiconductor device~~ of Claim 1, wherein the first and second active regions of the at least one semiconductor device are formed adjacent the first surface of the substrate of the at least one semiconductor device.
9. (Currently amended) The system ~~VLSI semiconductor device~~ of Claim 1, wherein dopants of the graded dopant concentration in the first active region or the second active region of the at least one semiconductor device are either p-type or n-type.
10. (Currently amended) The system ~~VLSI semiconductor device~~ of Claim 1, wherein dopants of the graded dopant concentration in the first active region of the at least one semiconductor device are both p-type and n-type.

11. (Currently amended) The system VLSI semiconductor device of Claim 1, wherein dopants of the graded dopant concentration in the second active region of the at least one semiconductor device are both p-type and n-type.
12. (Currently amended) The system VLSI semiconductor device of Claim 1, wherein dopants of the graded dopant region in the well region of the at least one semiconductor device are both p-type and n-type.
13. (Currently amended) The system VLSI semiconductor device of claim 1, wherein the transistors which can be formed in the first and second active regions of the at least one semiconductor device are CMOS digital logic transistors requiring at least a source, a drain, a gate and a channel.
14. (Currently amended) The system VLSI semiconductor device of Claim 1, wherein the at least one semiconductor device is a dynamic random access memory (DRAM).
15. (Currently amended) The system VLSI semiconductor device of Claim 1, wherein the at least one semiconductor device is a complementary metal oxide semiconductor (CMOS) with a nonepitaxial substrate.
16. (Currently amended) The system VLSI semiconductor device of Claim 1, wherein the at least one semiconductor device is a flash memory.
17. (Currently amended) The system VLSI semiconductor device of Claim 1, wherein the at least one semiconductor device comprises digital logic and capacitors.
18. (Currently amended) The system VLSI semiconductor device of Claim 1, wherein the at least one semiconductor device is a central processing unit.
19. (Currently amended) The system VLSI semiconductor device of Claim 1, wherein the at least one semiconductor device is an image sensor.

20. (Currently amended) The system ~~VLSI semiconductor device~~ of Claim 1, wherein each of the first and second active regions of the at least one semiconductor device are in the lateral or vertical direction.

21. (Currently amended) An electronic system ~~VLSI semiconductor device~~, comprising:
at least one semiconductor device, the at least one semiconductor device including:

a substrate of a first doping type at a first doping level having a surface;

a first active region disposed adjacent the surface of the substrate with a
5 second doping type opposite in conductivity to the first doping type and within
which transistors can be formed in the surface thereof;

a second active region separate from the first active region disposed
adjacent to the first active region and within which transistors can be formed in the
surface thereof;

10 transistors formed in at least one of the first active region or second active
region;

at least a portion of at least one of the first and second active regions having
at least one graded dopant concentration to aid carrier movement from the surface
to an area of the substrate where there are no active regions; and

15 at least one well region adjacent to the first or second active region
containing at least one graded dopant region, the graded dopant region to aid carrier
movement from the surface to the area of the substrate where there are no active
regions, and wherein the graded dopant concentration is linear, quasilinear, error
function, complementary error function, or any combination thereof.

22. (Currently amended) The system ~~VLSI semiconductor device~~ of Claim 21, wherein the
substrate of the at least one semiconductor device is an n-type substrate.

23. (Currently amended) The system ~~VLSI semiconductor device~~ of Claim 21, wherein the
substrate of the at least one semiconductor device is a p-type substrate.

24. (Currently amended) The system ~~VLSI semiconductor device~~ of Claim 21, wherein the substrate of the at least one semiconductor device has epitaxial silicon on top of a nonepitaxial substrate.
25. (Currently amended) The system ~~VLSI semiconductor device~~ of Claim 21, wherein the first active region and second active region of the at least one semiconductor device contain at least one of either p-channel and n-channel devices.
26. (Currently amended) The system ~~VLSI semiconductor device~~ of Claim 21, wherein the first active region and second active region of the at least one semiconductor device contain either p-channel or n-channel devices in n-wells or p-wells, respectively, and each well has at least one graded dopant.
27. (Currently amended) The system ~~VLSI semiconductor device~~ of Claim 21, wherein the first active region and second active region of the at least one semiconductor device are each separated by at least one isolation region.
28. (Currently amended) The system ~~VLSI semiconductor device~~ of Claim 21, wherein dopants of the graded dopant concentration in the first active region or the second active region of the at least one semiconductor device are either p-type or n-type.
29. (Currently amended) The system ~~VLSI semiconductor device~~ of Claim 21, wherein dopants of the graded dopant concentration in the first active region of the at least one semiconductor device are both p-type and n-type.
30. (Currently amended) The system ~~VLSI semiconductor device~~ of Claim 21, wherein dopants of the graded dopant concentration in the second active region of the at least one semiconductor device are both p-type and n-type.

REMARKS

Applicant has carefully reviewed the Office Action dated October 28, 2021. Applicant has amended Claims 1-30 to more clearly point out the present inventive concept. The amendments are supported by the specification as filed, such as in paragraph [0002]. No new matter has been added. Reconsideration and favorable action is respectfully requested.

Claims 1-30 were provisionally rejected under 35 U.S.C. § 101 as claiming the same invention as that of Claims 1-30 of co-pending Application No. 16/947,294 (“‘294” Application”). This rejection is respectfully traversed.

A reliable test for double patenting under 35 U.S.C. § 101 is whether a claim in the application could be literally infringed without literally infringing a corresponding claim in the patent. *See* MPEP § 804. Although a terminal disclaimer is not effective in overcoming a statutory double patenting rejection, the claims may be cancelled or amended so that they are not coextensive in scope. *Id.*

Applicant submits that Claims 1-30, as amended herein, are not coextensive in scope with the ‘294 Application. Accordingly, Applicant respectfully requests that the provisional double patenting rejection be withdrawn.

Applicant has now made an earnest attempt in order to place this case in condition for allowance. For the reasons stated above, Applicant respectfully requests full allowance of the claims as amended.

If any issues arise, or if the Examiner has any suggestions for expediting allowance of this Application, the Applicant respectfully invites the Examiner to contact the undersigned at the telephone number indicated below or at whowison@munckwilson.com.

Recognizing that Internet communications are not secure, Applicant hereby authorizes the USPTO to communicate with the undersigned and practitioners in accordance with 37 CFR 1.33 and 37 CFR 1.34 concerning any subject matter of this application by video conferencing, instant

messaging, or electronic mail. Applicant understands that a copy of these communications will be made of record in the application file.

Please charge any additional fees or deficiencies in fees or credit any overpayment to Deposit Account No. 50-0208/GRTD60-35314.

Respectfully submitted,
MUNCK WILSON MANDALA, LLP
Attorneys for Applicant

/William G. Howison, Reg. #66850/

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WGH/als

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December 1, 2021

Electronic Acknowledgement Receipt

EFS ID:	44406378
Application Number:	17371839
International Application Number:	
Confirmation Number:	2197
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS
First Named Inventor/Applicant Name:	G.R. MOHAN RAO
Customer Number:	25883
Filer:	William G. Howison
Filer Authorized By:	
Attorney Docket Number:	GRTD60-35314
Receipt Date:	01-DEC-2021
Filing Date:	09-JUL-2021
Time Stamp:	19:00:40
Application Type:	Utility under 35 USC 111(a)

Payment information:

Submitted with Payment	no
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File Listing:

Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)
1		GRT35314AMD.pdf	123821	yes	8
			6ce164b4363ce2aead4fe55db6433770dad9b708		

	Multipart Description/PDF files in .zip description		
	Document Description	Start	End
	Amendment/Req. Reconsideration-After Non-Final Reject	1	1
	Claims	2	6
	Applicant Arguments/Remarks Made in an Amendment	7	8

Warnings:

Information:

Total Files Size (in bytes):	123821
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New Applications Under 35 U.S.C. 111

If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.

National Stage of an International Application under 35 U.S.C. 371

If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.

New International Application Filed with the USPTO as a Receiving Office

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PATENT APPLICATION FEE DETERMINATION RECORD Substitute for Form PTO-875				Application or Docket Number 17/371,839		Filing Date 07/09/2021		☐ To be Mailed			
ENTITY: ☒ LARGE ☐ SMALL ☐ MICRO											
APPLICATION AS FILED - PART I											
		(Column 1)		(Column 2)							
FOR		NUMBER FILED		NUMBER EXTRA		RATE (\$)		FEE (\$)			
☐ BASIC FEE (37 CFR 1.16(a), (b), or (c))		N/A		N/A		N/A					
☐ SEARCH FEE (37 CFR 1.16(k), (i), or (m))		N/A		N/A		N/A					
☐ EXAMINATION FEE (37 CFR 1.16(o), (p), or (q))		N/A		N/A		N/A					
TOTAL CLAIMS (37 CFR 1.16(i))		minus 20 = *				x \$100 =					
INDEPENDENT CLAIMS (37 CFR 1.16(h))		minus 3 = *				x \$480 =					
☐ APPLICATION SIZE FEE (37 CFR 1.16(s))		If the specification and drawings exceed 100 sheets of paper, the application size fee due is \$310 (\$155 for small entity) for each additional 50 sheets or fraction thereof. See 35 U.S.C. 41(a)(1)(G) and 37 CFR 1.16(s).									
☐ MULTIPLE DEPENDENT CLAIM PRESENT (37 CFR 1.16(j))											
* If the difference in column 1 is less than zero, enter "0" in column 2.						TOTAL					
APPLICATION AS AMENDED - PART II											
		(Column 1)		(Column 2)		(Column 3)					
AMENDMENT	12/01/2021	CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR		PRESENT EXTRA		RATE (\$)		ADDITIONAL FEE (\$)	
	Total (37 CFR 1.16(i))	* 30	Minus	** 30	= 0			x \$100 =		0	
	Independent (37 CFR 1.16(h))	* 2	Minus	*** 3	= 0			x \$480 =		0	
	☐ Application Size Fee (37 CFR 1.16(s))										
	☐ FIRST PRESENTATION OF MULTIPLE DEPENDENT CLAIM (37 CFR 1.16(j))										
								TOTAL ADD'L FEE		0	
		(Column 1)		(Column 2)		(Column 3)					
AMENDMENT		CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR		PRESENT EXTRA		RATE (\$)		ADDITIONAL FEE (\$)	
	Total (37 CFR 1.16(i))	*	Minus	**	=			x \$0 =			
	Independent (37 CFR 1.16(h))	*	Minus	***	=			x \$0 =			
	☐ Application Size Fee (37 CFR 1.16(s))										
	☐ FIRST PRESENTATION OF MULTIPLE DEPENDENT CLAIM (37 CFR 1.16(j))										
								TOTAL ADD'L FEE			
* If the entry in column 1 is less than the entry in column 2, write "0" in column 3.								LIE			
** If the "Highest Number Previously Paid For" IN THIS SPACE is less than 20, enter "20".								/TINA M. BELL/			
*** If the "Highest Number Previously Paid For" IN THIS SPACE is less than 3, enter "3".											
The "Highest Number Previously Paid For" (Total or Independent) is the highest number found in the appropriate box in column 1.											

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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
17/371,839	07/09/2021	G.R. MOHAN RAO	GRTD60-35314	2197
25883	7590	01/31/2022		
MUNCK WILSON MANDALA L.L.P			EXAMINER	
P.O. Drawer 800889			ARORA, AJAY	
DALLAS, TX 75380				
			ART UNIT	PAPER NUMBER
			2892	
			NOTIFICATION DATE	DELIVERY MODE
			01/31/2022	ELECTRONIC

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Notice of the Office communication was sent electronically on above-indicated "Notification Date" to the following e-mail address(es):

IPdocketing@munckwilson.com
admin@dalpat.com
eofficeaction@appcoll.com



UNITED STATES PATENT AND TRADEMARK OFFICE

Commissioner for Patents
United States Patent and Trademark Office
P.O. Box 1450
Alexandria, VA 22313-1450
www.uspto.gov

In re Application of :
RAO, G.R. MOHAN :
Application No. 17/371,839 : **DECISION ON PETITION**
Filed: 9 Jul 2021 :
For: SEMICONDUCTOR DEVICES WITH :
GRADED DOPANT REGIONS :

This is a decision on the petition under 37 CFR 1.182 filed October 19, 2021, to expunge an assignment previously recorded against the above-identified application. In particular, the petitioner requests that Assignment 2, i.e., from Greenthread, LLC to Vervain, LLC be expunged.

The petition to expunge the assignment documents is **DISMISSED**. This is not a final agency action.

As discussed in the *Manual of Patent Examining Procedure* (MPEP) § 323.01(d), petitions to correct, modify or "expunge" assignment records are **rarely** granted. Such petitions are granted only if the petitioner can prove that:

- (A) the normal corrective procedures outlined in MPEP § 323.01(a) through § 323.01(c) will not provide the petitioner with adequate relief; and
- (B) the integrity of the assignment records will not be affected by granting the petition.

The petition has not proven either item (A) or (B).

In regard to item (A), petitioner asserts that the corrective procedures outlined in MPEP § 323.01(a) through § 323.01(c) will not provide adequate relief. In particular, petitioner argues that MPEP § 323.01(a) and (b) do not apply because the recordation error is not a typographical error and matches the cover sheet. Further, petitioner argues that MPEP § 323.01(c) does not apply because the assignment was not improperly filed and recorded by another person against the above-identified application. These arguments are not persuasive as the corrective procedures outlined in MPEP § 323.01(a) through § 323.01(c) are not limited to only minor or typographical errors in filing. A corrective document may be recorded as set forth below.

Furthermore, in regard to item (B), petitioner contends that the integrity of the assignment records will not be affected by the desired expungement. However, the removal of a document in its entirety, as requested, will affect the assignment records. The integrity of the records is recognized as separate from the chain of title. Expungement would prevent the records from being searchable in the Assignment Historical Database or otherwise available to the public, which may be necessary for a competent authority to determine the proper chain of title. Moreover, the expungement requested involves a validity determination by the USPTO regarding the information to be expunged, which may impact ownership claims on the related patent. The USPTO, however, has no authority to decide ownership issues. *See Cedars-Sinai Medical Center v. Watkins*, 11F.3d 1573, 1581 n.10, 29 USPQ 2d 1188, 1194 n.10 (Fed. Cir. 1993), *cert. denied*, 114 S. Ct. (1994). Rather, state law governs contractual obligations, including patent assignment agreements. *See Intellectual Ventures I LLC v. Erie Indem. Co.*, 121 USPQ2d 1928, 1930 (Fed. Cir. 2017); *In re Haines*, 1900 C.D. 102, 103 (Comm'r Pat. 1900). While the ownership of patent rights is typically a question exclusively for state courts, the question of whether contractual language effects a present assignment agreement of patent rights, or an agreement to assign rights in the future, is resolved by Federal Circuit law. *See Abraxis Bioscience Inc. v. Navinta LLC*, 96 USPQ2d 1977, 1981 (Fed. Cir. 2010); *Speedplay, Inc. v. Bebbo, Inc.*, 211 F.3d 1245, 1253 [53USPQ2d 1984] (Fed. Cir. 2000).

35 U.S.C. § 261 provides the USPTO with only the limited authority to maintain the assignment records, and does not grant the USPTO with the authority to remove documents.

Petitioner should note that, as discussed in MPEP § 323.01(d),

“Even if a petition to “expunge” a document is granted with respect to a particular application or patent, the image of the recorded document will remain in the records of the Assignment Services Division at the same reel and frame number, and the image will appear when someone views that reel and frame number.”

In the context of the assignment records, “expunge” does not mean that a document will be removed in its entirety. Rather, “expunge” means that a document containing sensitive information, such as a Social Security Number, may be replaced in the electronically searchable records with a redacted copy of the same document. The original document will remain in the assignment records at the reel/frame number given without redaction. Through “expungement,” the electronic links between the document and the application will be deleted so the original document is no longer available through an electronic search.

As background, the USPTO simply acts in a ministerial capacity in recording documents that have been submitted for recordation. *See* 35 USC 261 and 37 CFR 3.11. However, the recording of a document pursuant to 37 CFR 3.11 is **not** a determination by the USPTO of the validity of the document *per se* or the effect that document has on the title to a patent or application. *See* 37 CFR 3.54. Moreover, it is USPTO policy to maintain a complete history of claimed interests in a